

Программа Фонда Дмитрия Зимина «Династия»  
„Краткосрочные визиты иностранных ученых в  
Россию“

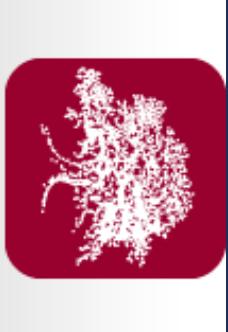


iphf jena



# Wet Chemically Etched Silicon Nanowires: A Key Component in New Generation of Energy Devices

Династия



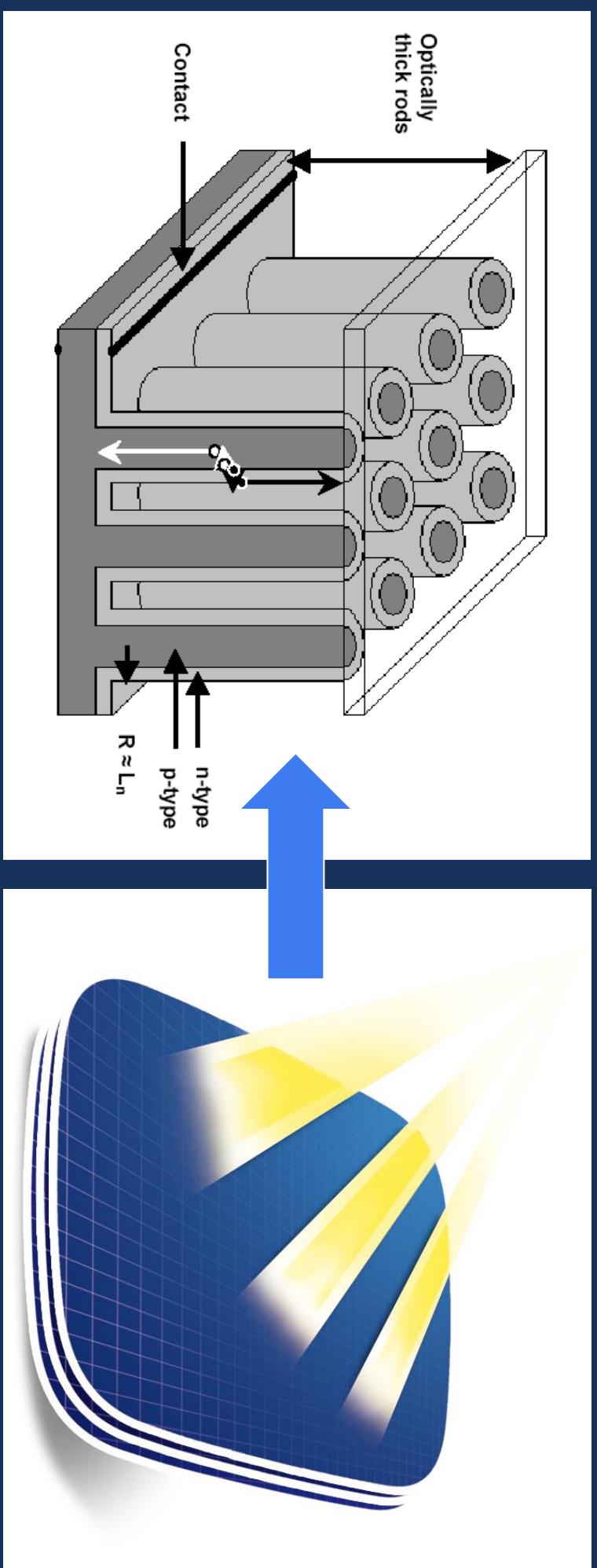
Vladimir Sivakov

*Leibniz Institute of Photonic Technology,  
Jena/Germany*



# Outline

1. Top-down *vs* Bottom-up
2. 3 Keys for Novel Photovoltaic Devices
3. Photovoltaic Concepts Based on SiNWs
4. Solar Hydrogen

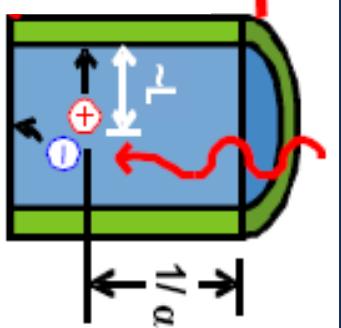


**Si Nanowires:**  $\eta=15\text{-}20\%$

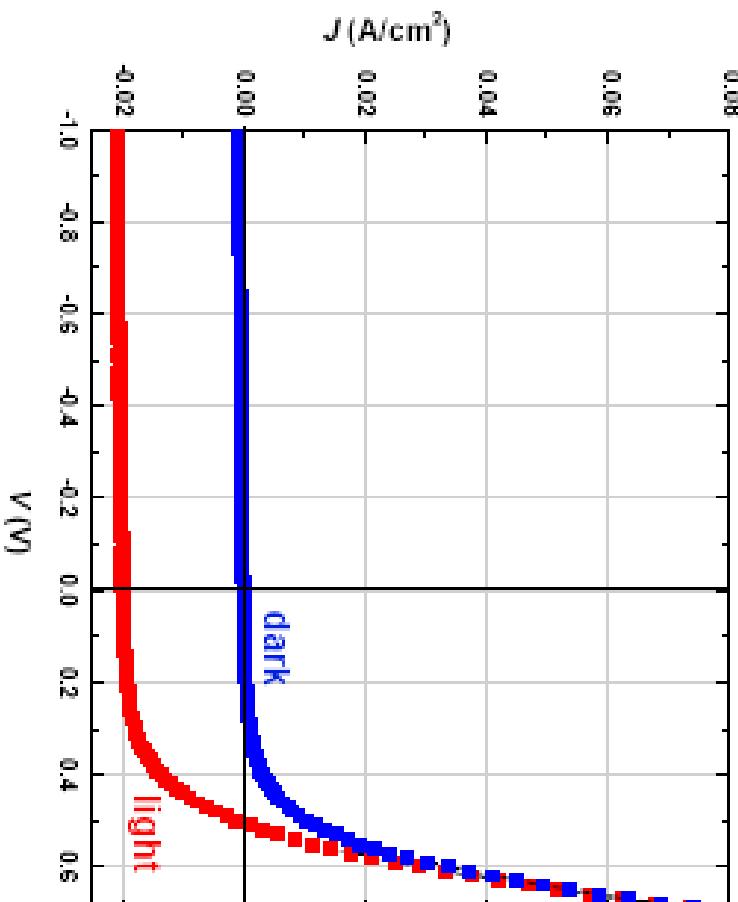
**mc-Si thin film:**  $\eta=6\text{-}10\%$

B.M. Kayes, H.A. Atwater, N.S. Lewis, J. Appl. Phys. **97**, 114302 (2005); B.M. Kayes, M.A. Filler, M.C. Putnam, M.D. Kelzenberg, N.S. Lewis, H.A. Atwater, Appl. Phys. Lett. **91**, 103110 (2007); L. Tsakalakos, J. Balch, J. Fronheiser, B.A. Korevaar, O. Sulima, J. Rand, Appl. Phys. Lett. **91**, 233117 (2007); M.D. Kelzenberg, D.B. Turner-Evans, B.M. Kayes, M.A. Filler, M.C. Putnam, N.S. Lewis, H.A. Atwater, Nano Lett. **8**, 710 (2008)

# Solar Cell Based on SiNWs



of the radial pn junction on the top surface. Infrareds of the high-aspect ratio wires are optically thick (thick), so the collection coefficient of the minority carriers are less than unity.



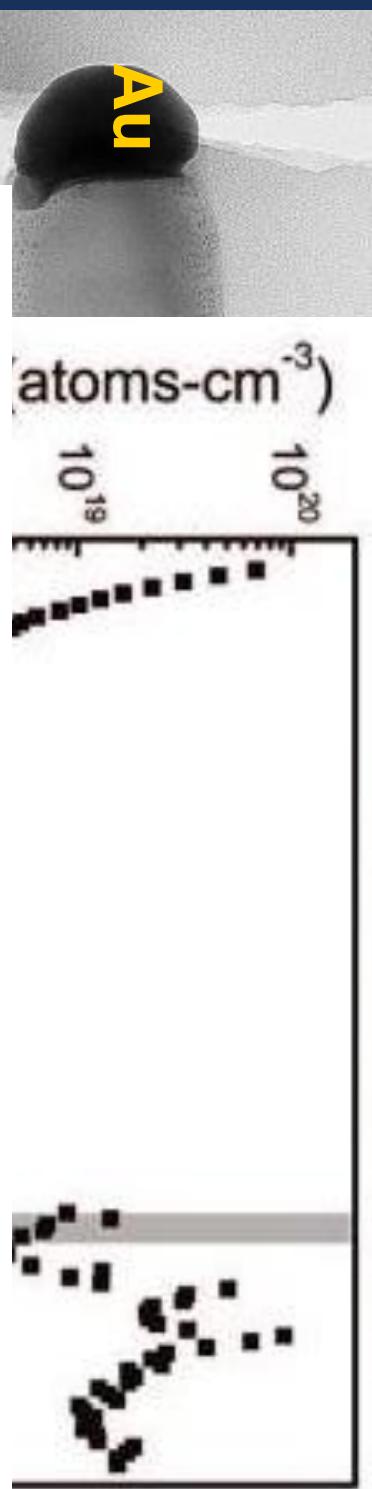
**Fig. 4.**  $J$ - $V$  curve for measured 5  $\mu\text{m}$ -diameter wire array. Efficiency = 5.7 %,  $V_{oc} = 505 \text{ mV}$ ,  $J_{sc} = 19.7 \text{ mA/cm}^2$ ,  $FF = 57.7 \%$ , total cell area  $12.9 \text{ mm}^2$ , wire array area  $4 \text{ mm}^2$ .

M.D. Kelzenberg et al., Nano Lett. 8, 710 (2008)

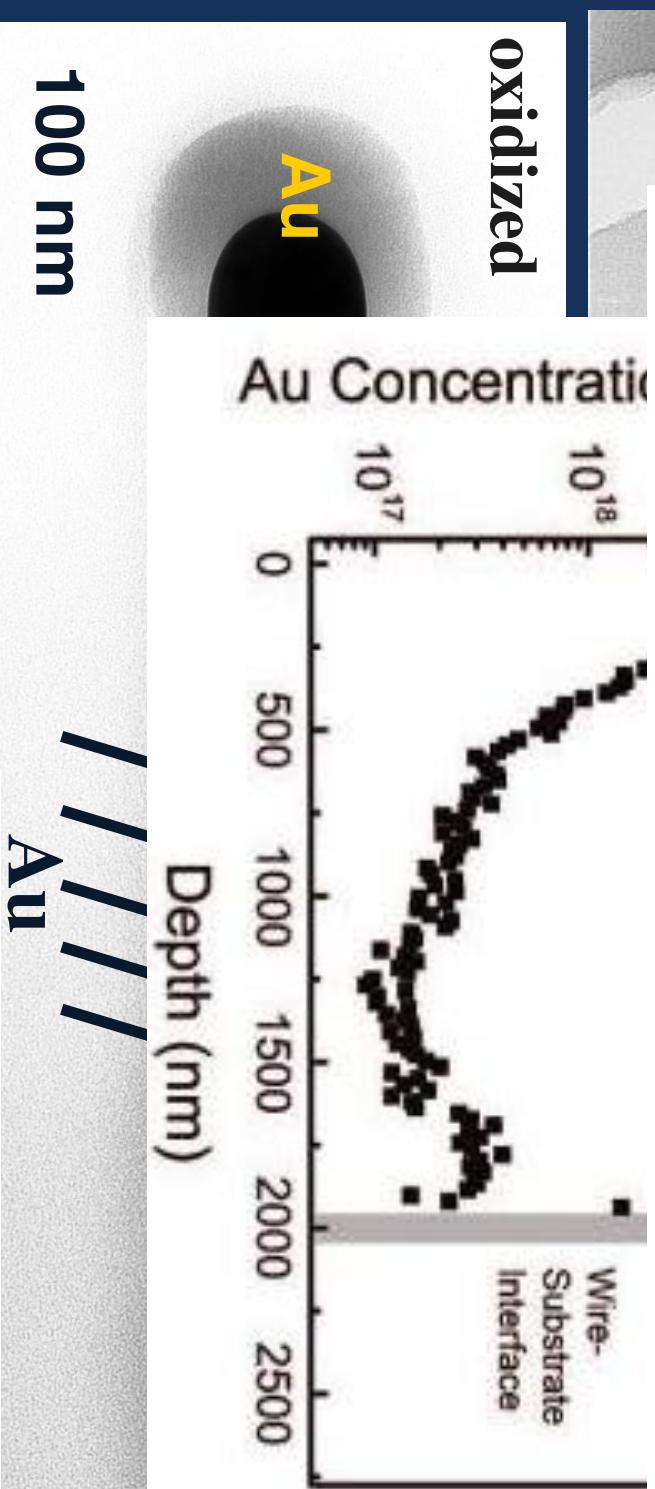
# Problematic: Gold Contamination

as deposited

Radial: Un-etched Wire



Potential limits to electrical and optical device performance



100 nm

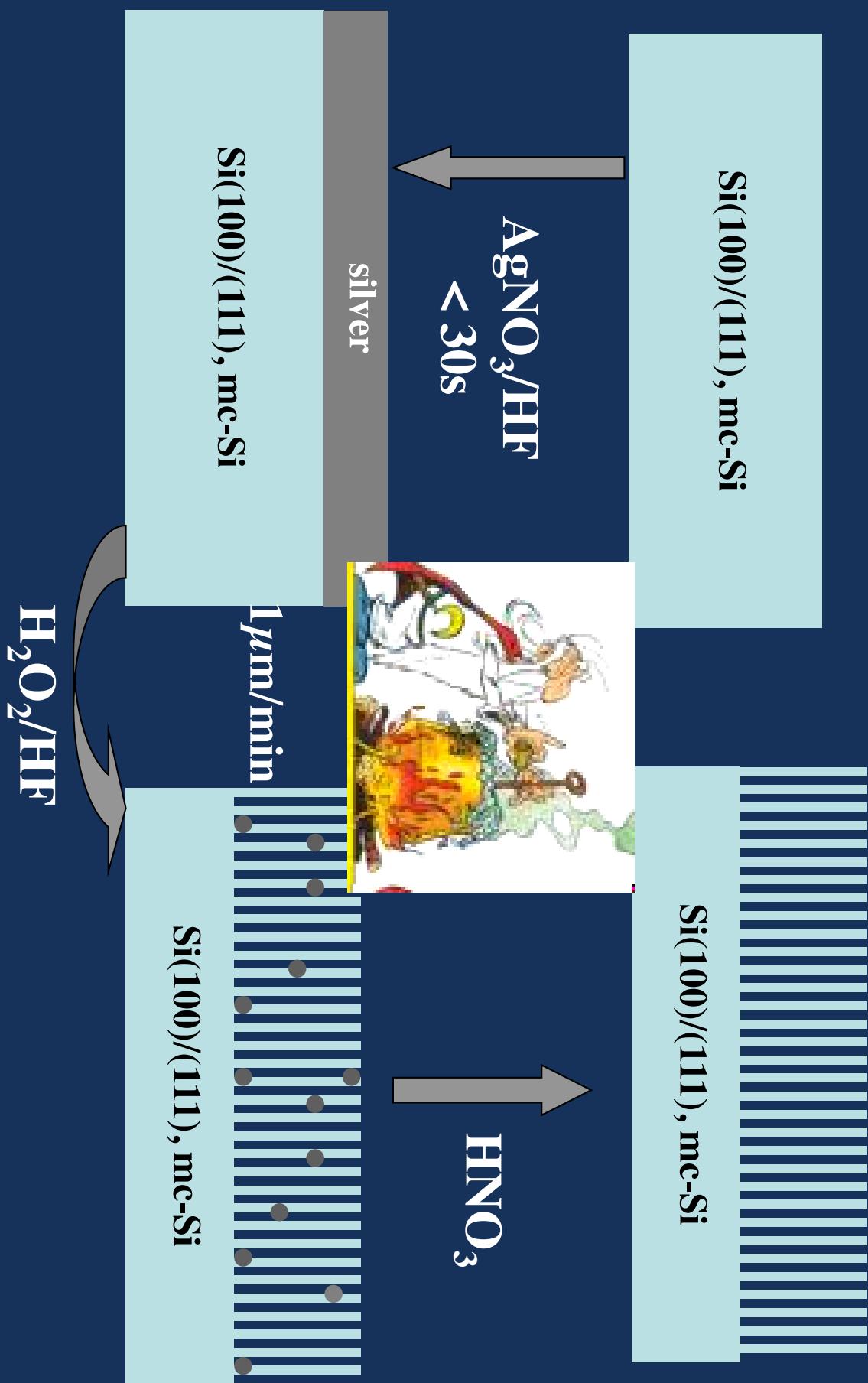
/// Au

## Motivation

- ✓ Smart Material
- ✓ Smart Technology
- Smart Concept



# Top-down: Wet-Chemical Etching

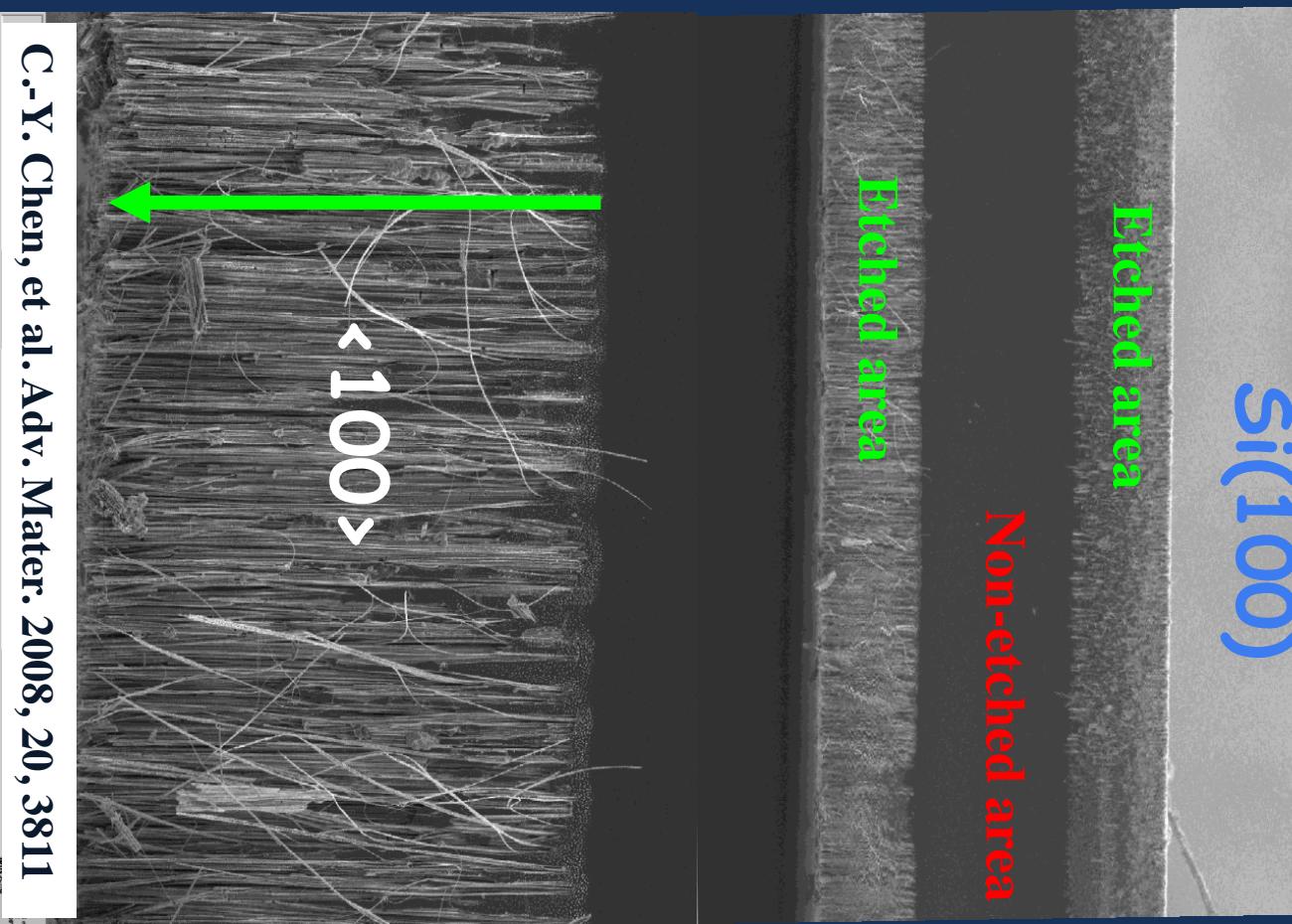
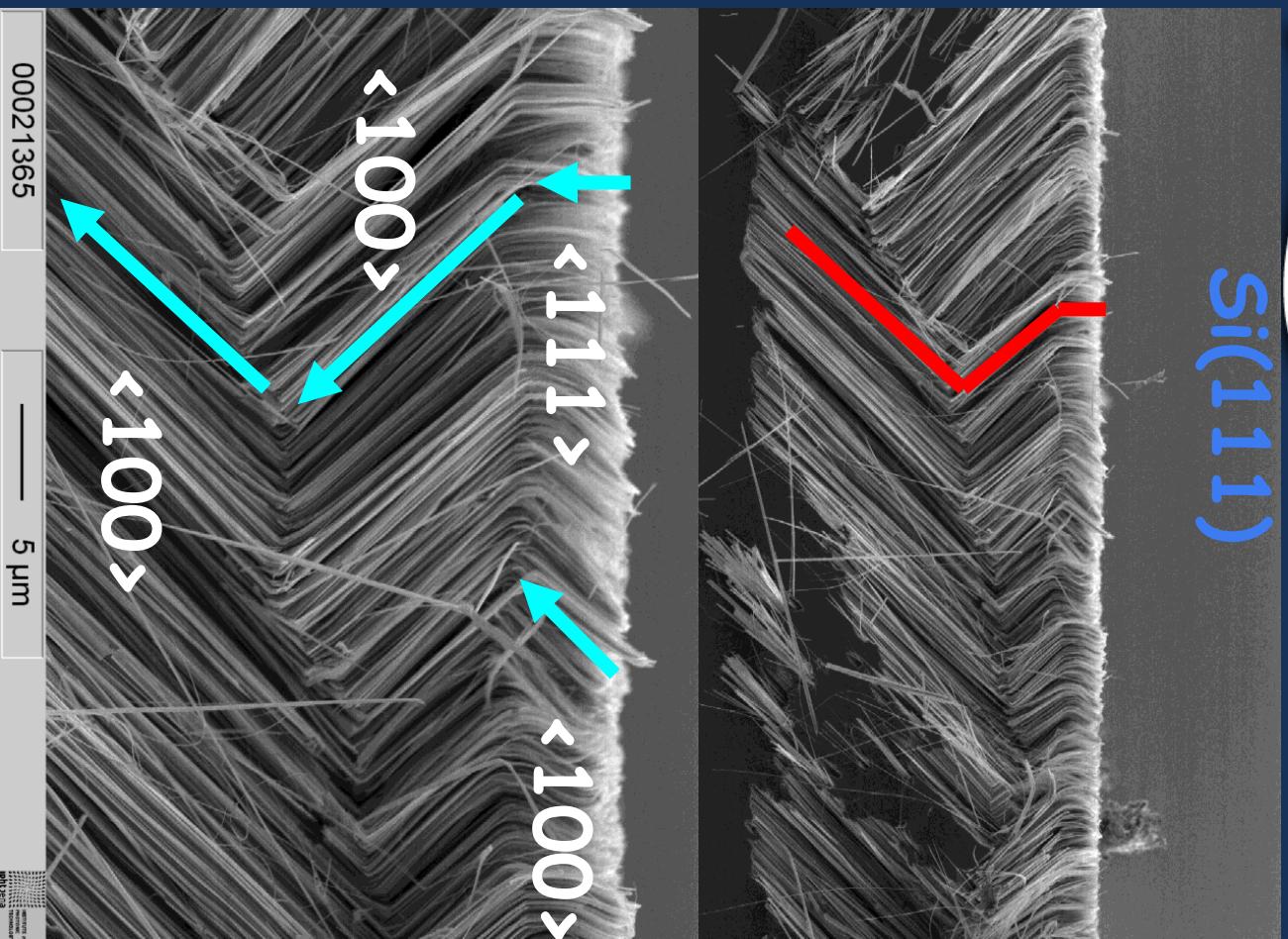


V.A. Sivakov et al., J. Phys. Chem. C 14, 3798–3803 (2010)  
V. Sivakov et al., Intech "Nanowires - Fundamental Research", ISBN 978-953-307-327-9, p45 (2011)  
Dr. Vladimir Sivakov, IPHT  
06.03.2014

# Top-down: Wet-Chemical Etching

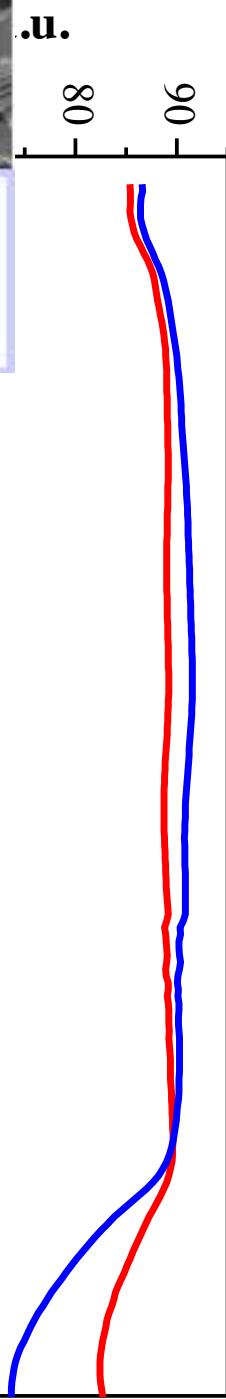
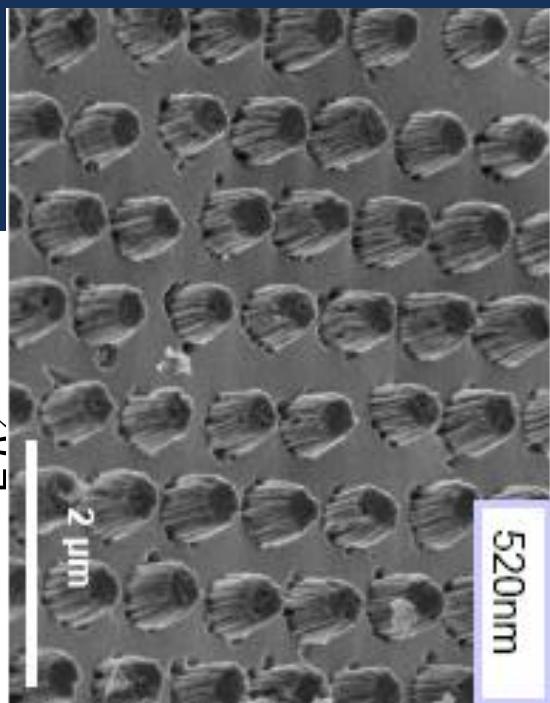
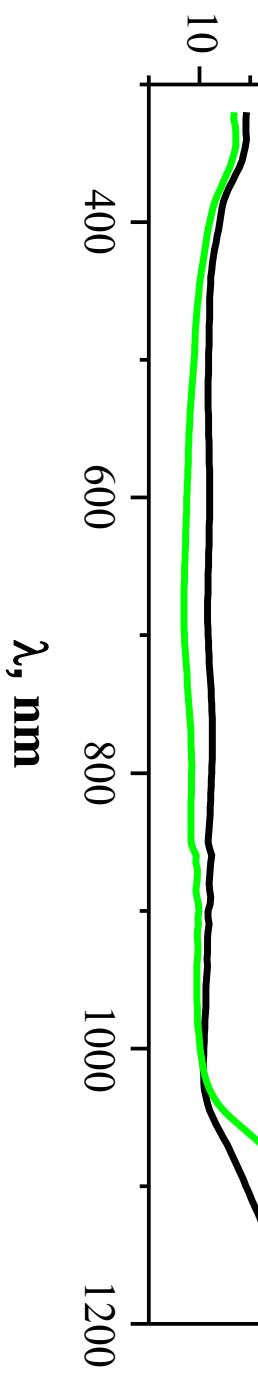
Si(111)

Si(100)

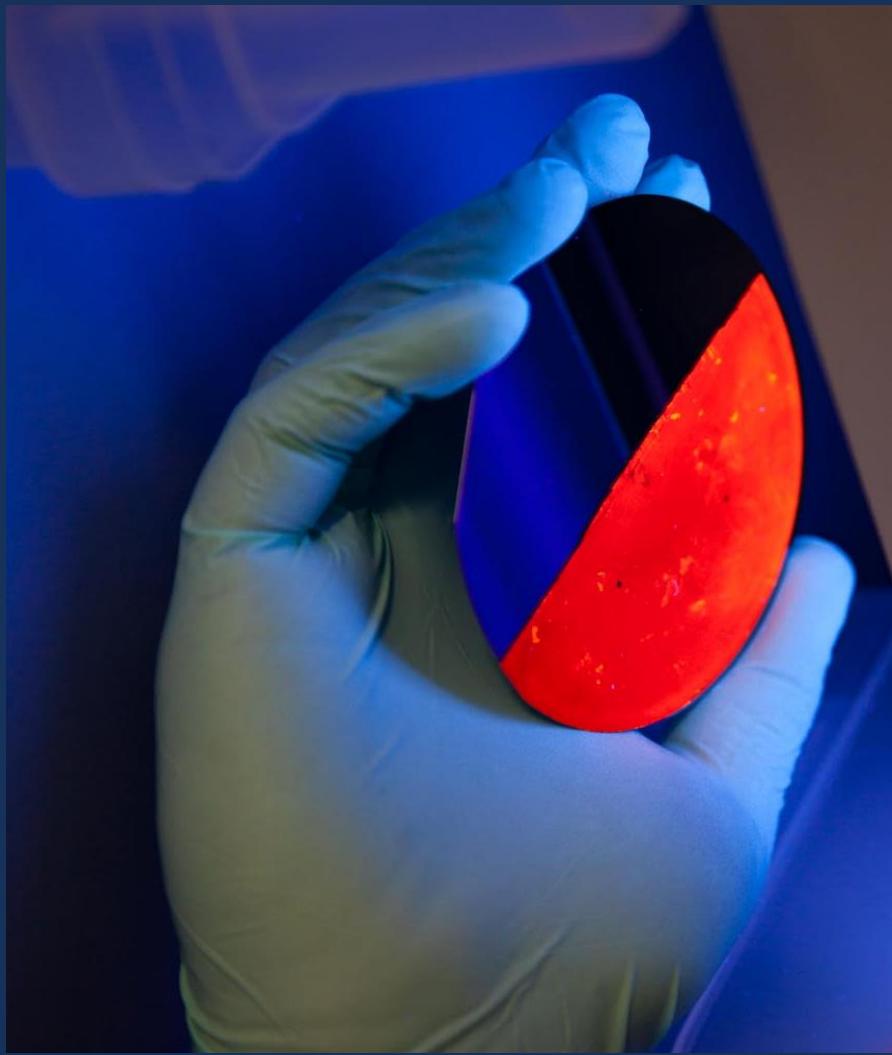
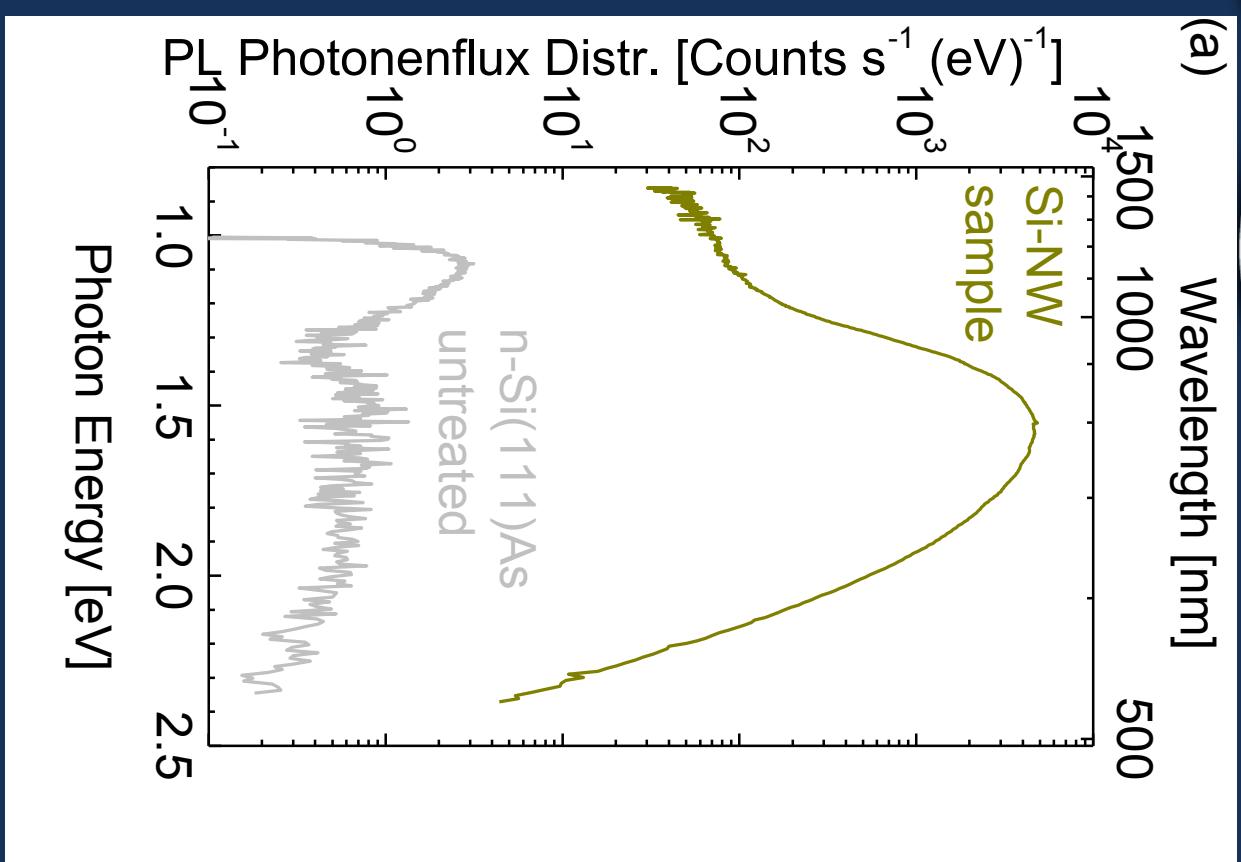


# Top-down: Wet-Chemical Etching

$$A = I - R - T$$



# Top-down: Wet-Chemical Etching



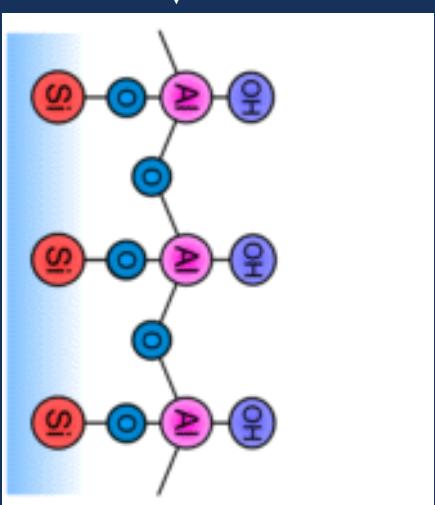
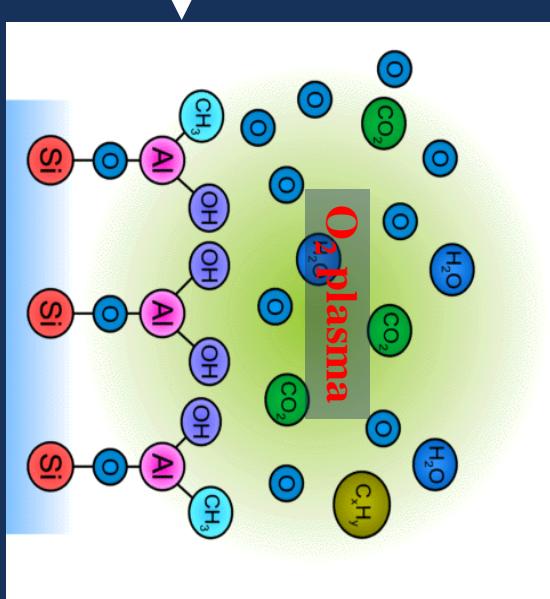
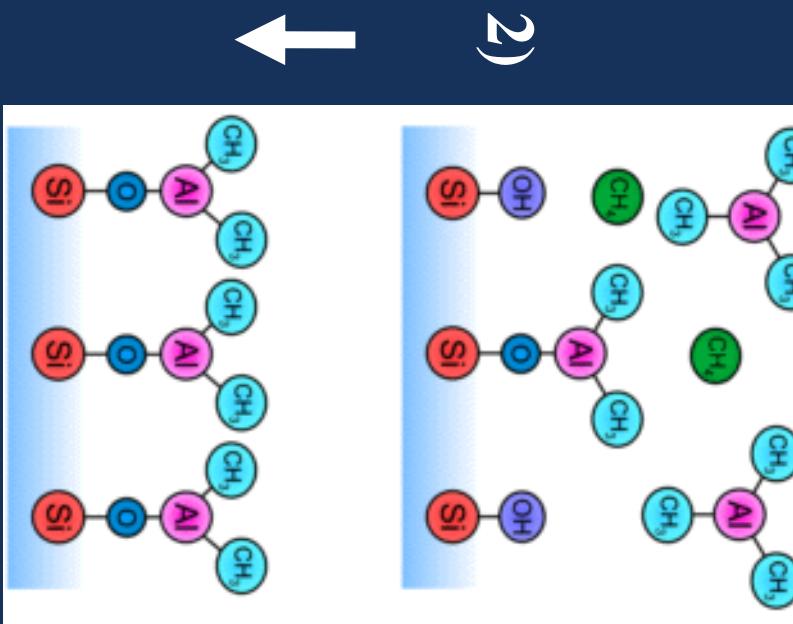
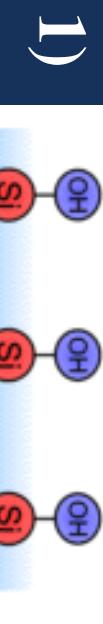
V.A. Sivakov et al. Phys. Rev. B 82, 125446(2010)

## Motivation

- ✓ Smart Material
- ✓ Smart Technology
- Smart Concept



# ALD Technology



1. Component 1(TMAl, Al(CH<sub>3</sub>)<sub>3</sub>)
2. Purge (Ar)
3. Oxidant: H<sub>2</sub>O / Plasma: O<sub>2</sub>
4. Purge (Ar)

Cycle

Smart technology



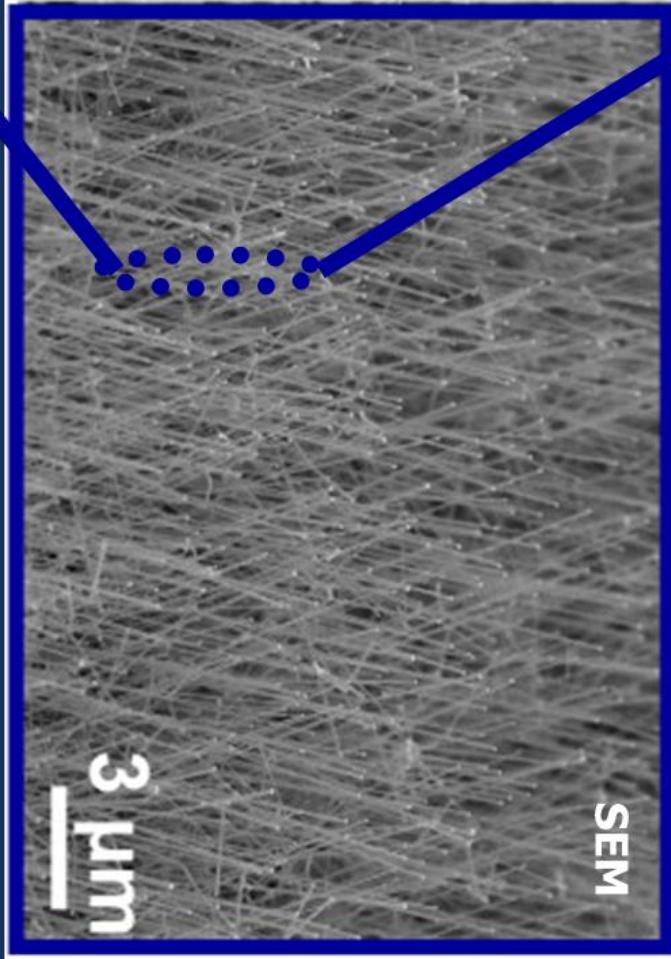
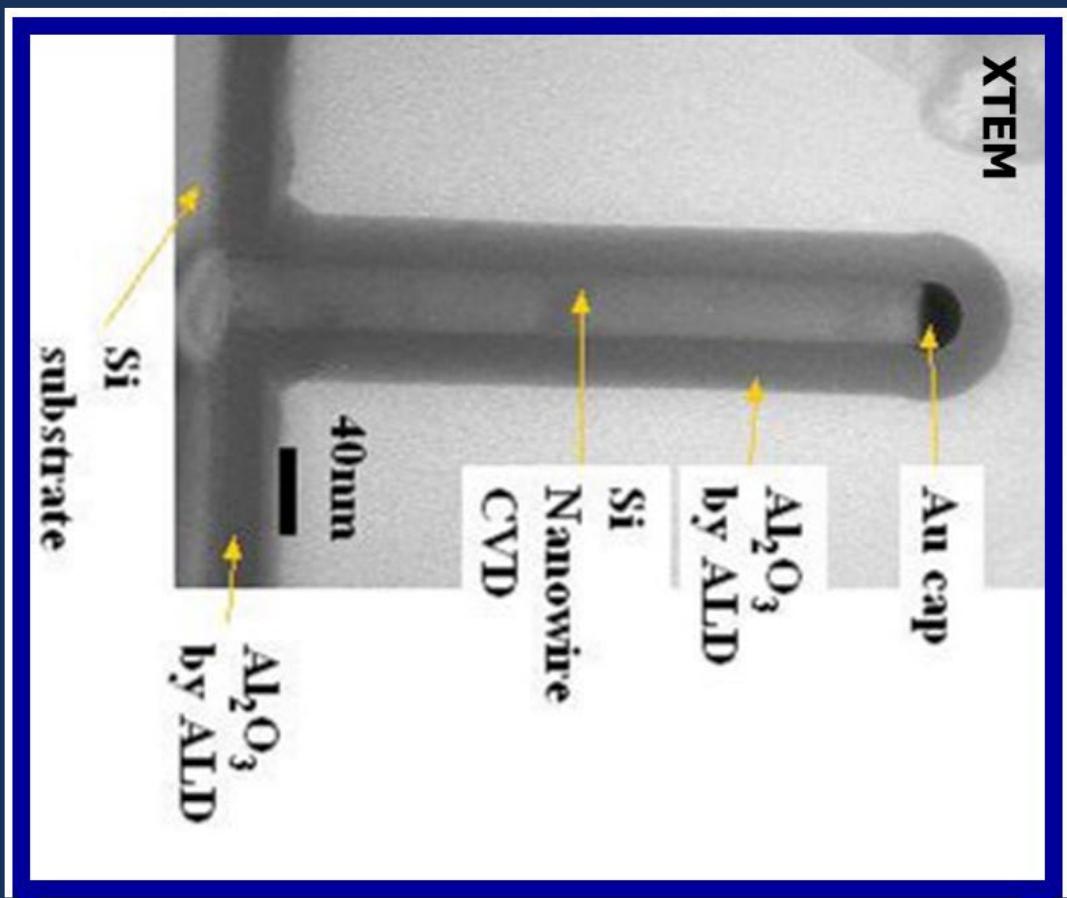
3)  
Purge

Dr. Vladimir Sivakov, IPHT

4)  
O<sub>2</sub> plasma  
06.03.2014

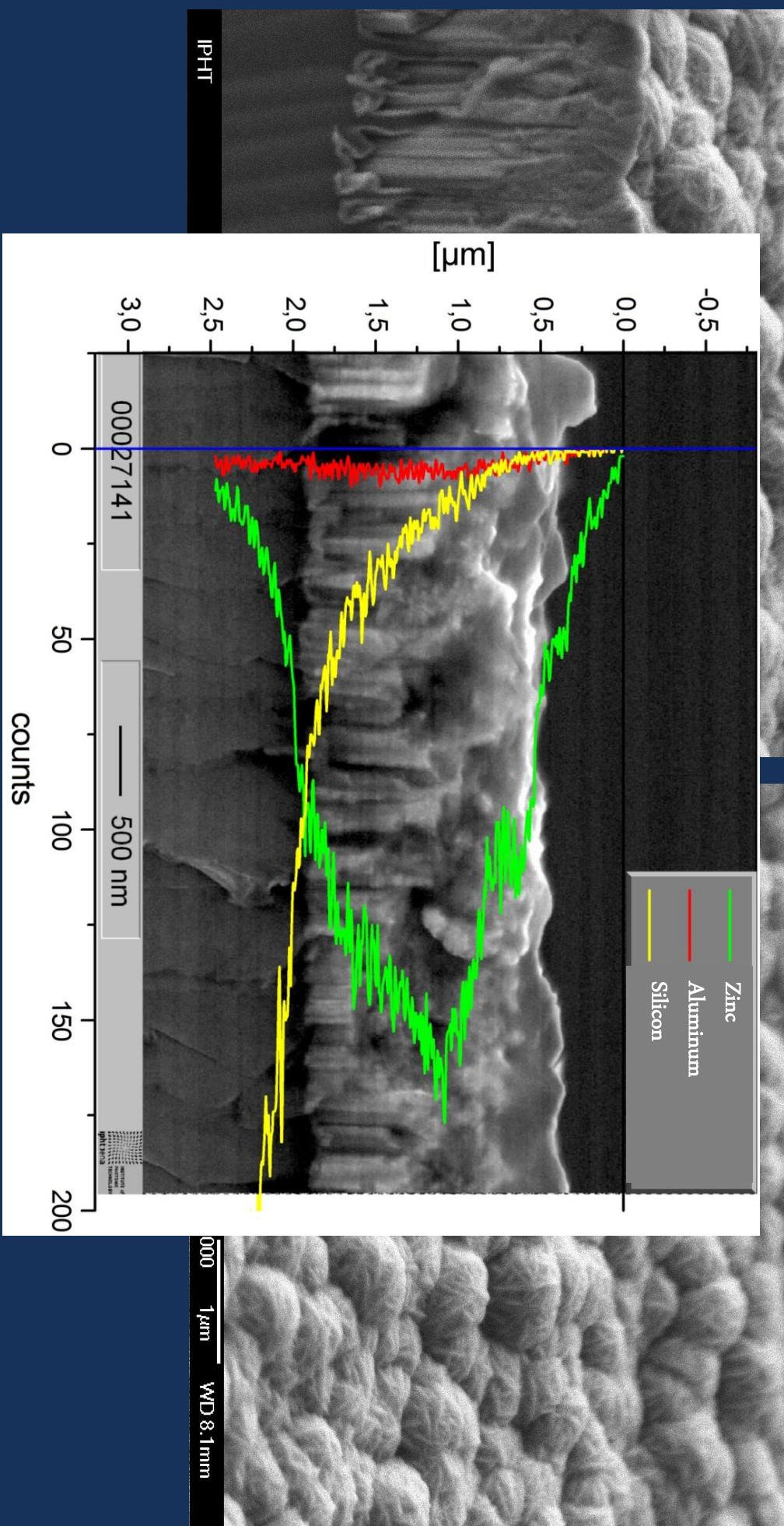
5)  
Purge

# ALD Technology



ALD: Gao, Ley, Physik, Uni Erlangen

# ALD Technology



Very homogeneous distribution of ZnO inside the nanowire carpet

## Application examples:

- Organic light emitting diodes (OLED)
- Liquid crystal displays (LCD)
- Touch panels
- Thin film solar cells



## Aluminium Zinc Oxide

- Low specific resistivity:  $\sim 10^{-5}$   $\Omega\text{cm}$
- Present specific resistivity:  $\sim 10^{-4}$   $\Omega\text{cm}$
- Better transmission in visible range
  - Low cost

## Indium Tin Oxide

## Farbication of Al doped ZnO using Atomic Layer Deposition

### Precursors:

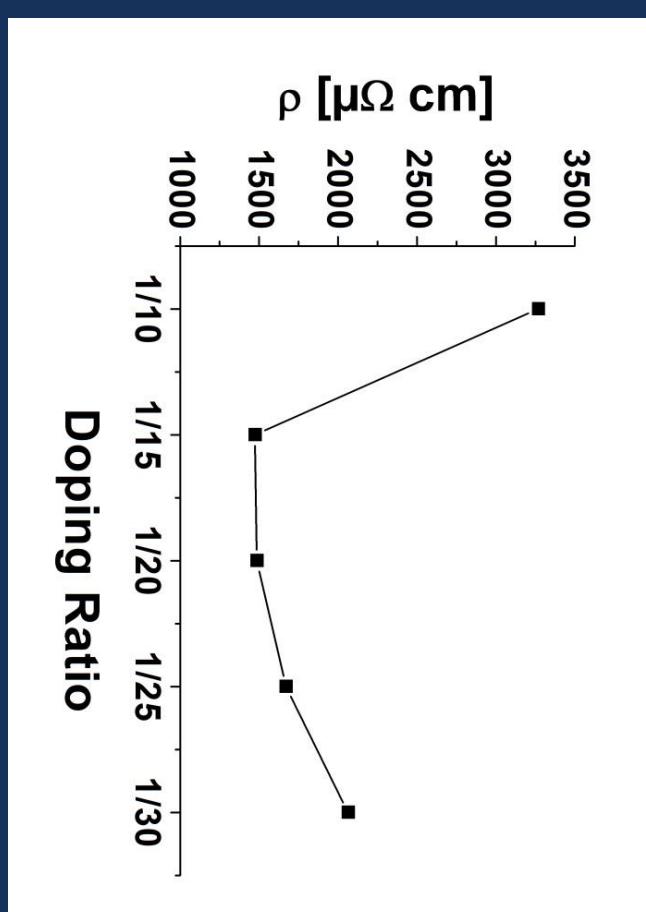
- Diethylzinc (DEZ)
- Trimethylaluminium (TMA)
- Water ( $H_2O$ )

Doping Sequence:  
N cycles DEZ/ $H_2O$  + 1 cycle TMA/ $H_2O$

Minimal specific resistivity:

$8 \times 10^{-4} \Omega \text{ cm}$

Stoichiometry measurement (with RBS):



### Best results:

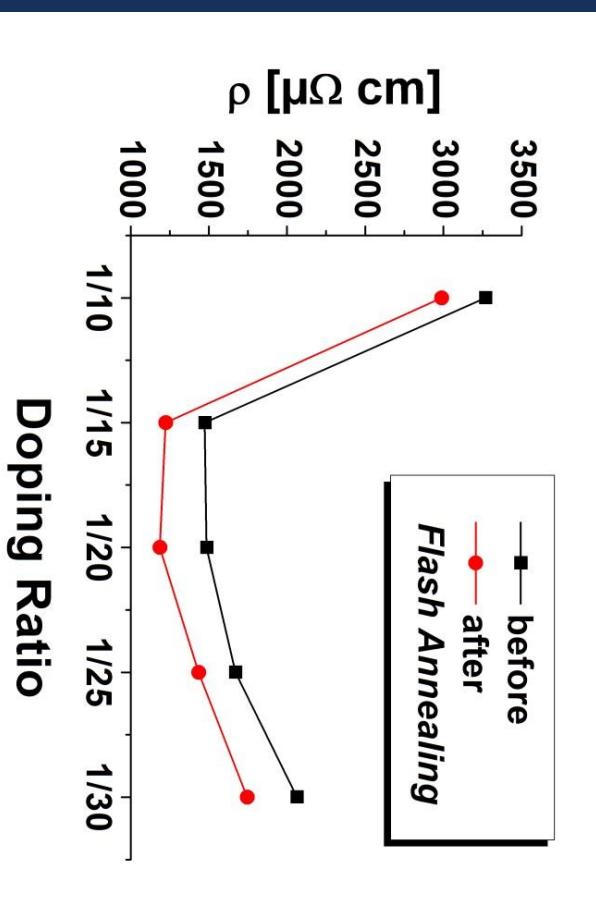
- temperatures  $\geq 200^\circ C$
- $1/15 \geq \text{best ratio} \geq 1/20$

## Flash Annealing

Flash Annealing System:

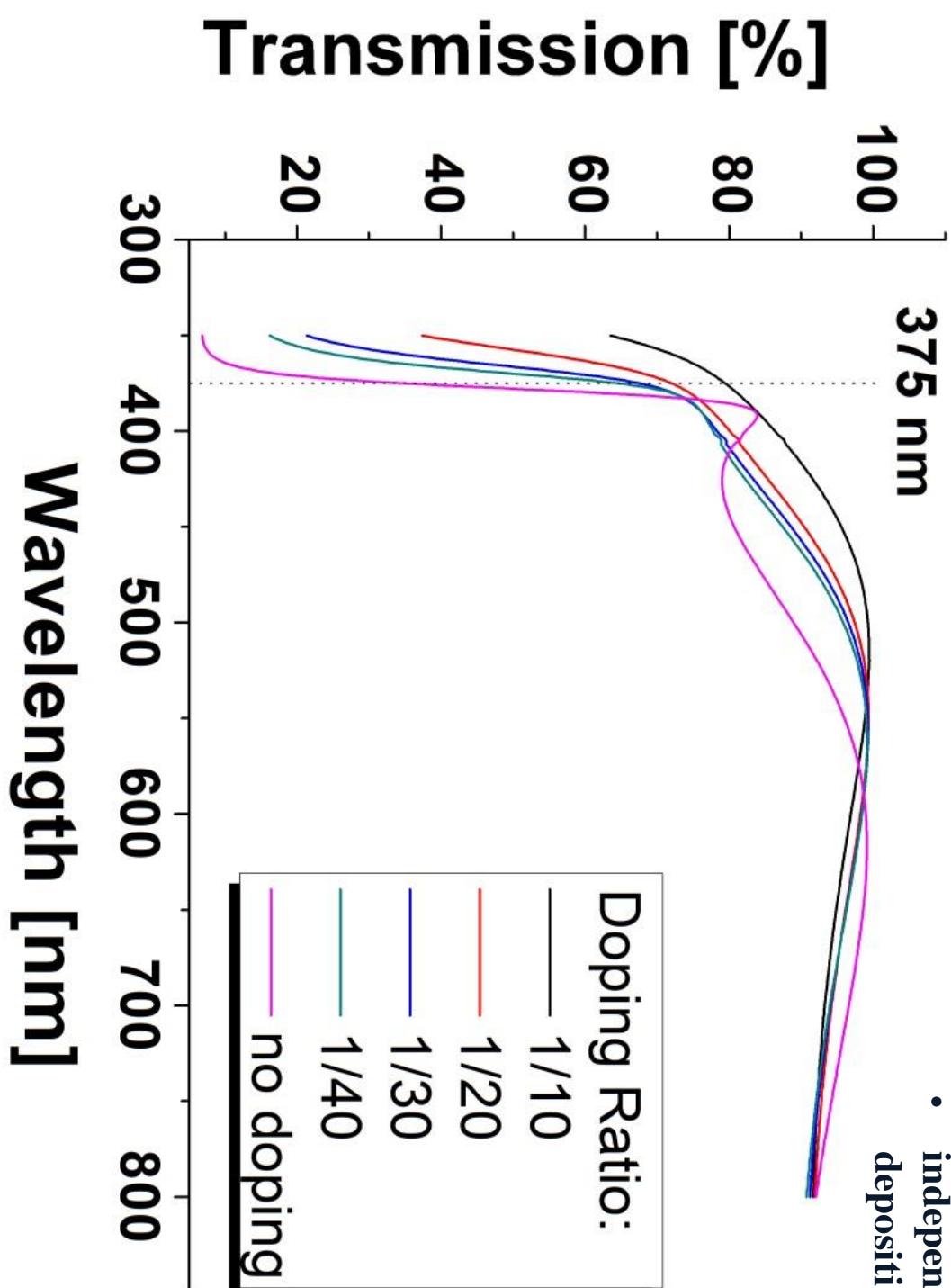


- Short impulslength of a few hundred microseconds
- High energy up to  $120 \text{ J/cm}^2$
- temperature sensitiv substrates possible



# Transparent Conductive Oxides (TCO)

- Band gap: ~3.3 eV (375 nm)
- about 90 % in visible range
- independent of doping and deposition temperature



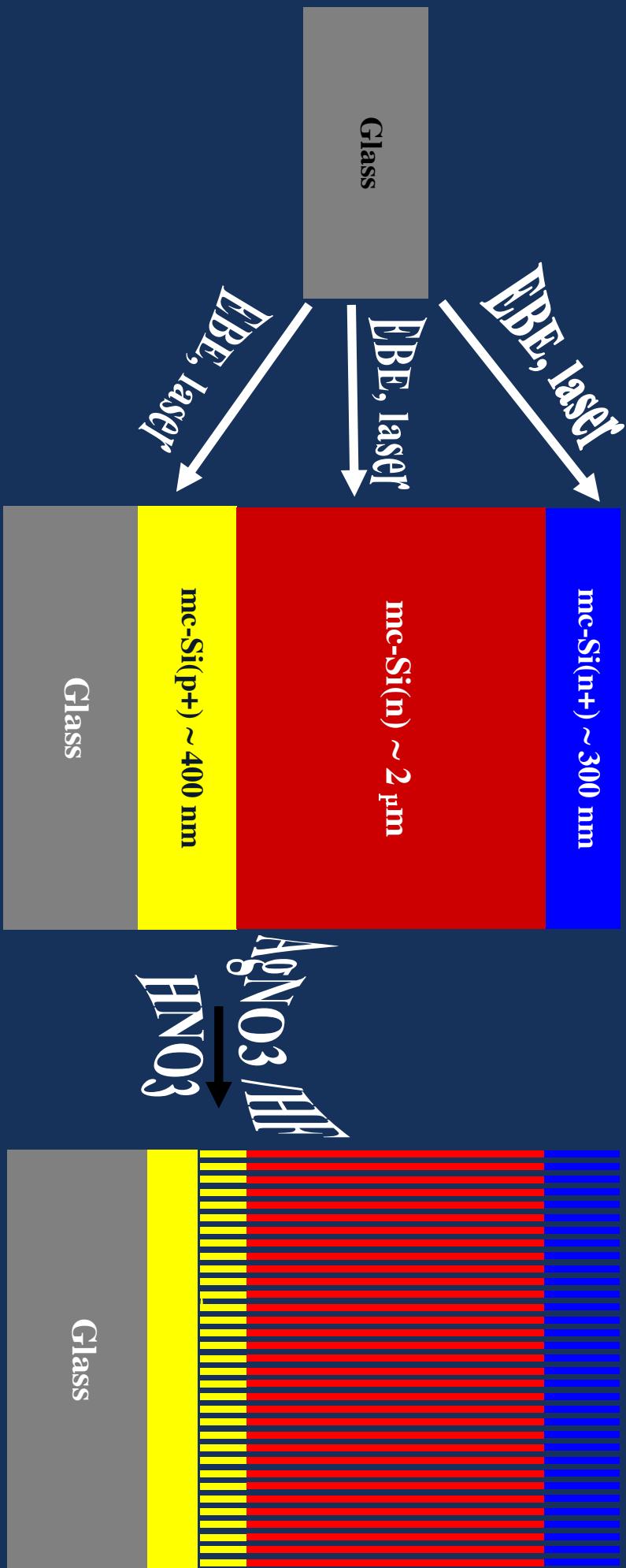
## Motivation

- ✓ Smart Material
- ✓ Smart Technology
- ✓ Smart Concept



# Photovoltaic Concept I

# Solar Cell Based on VLS SiNWs

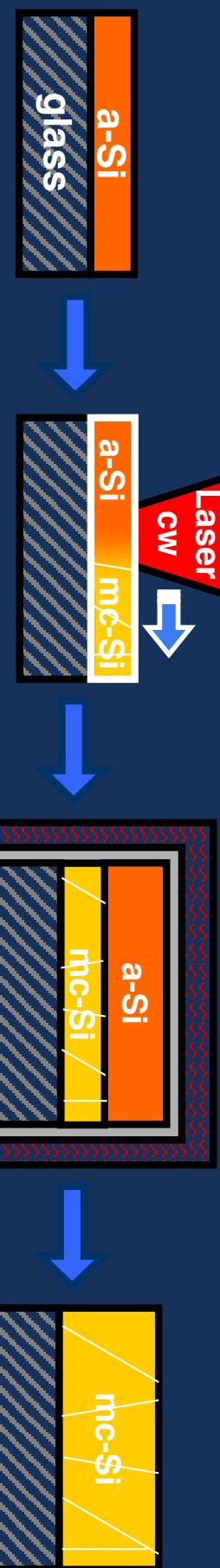


Schematic cross sectional view of the mc-Si p-n junction layer stack on a glass substrate before and after “Black Etch” treatment.

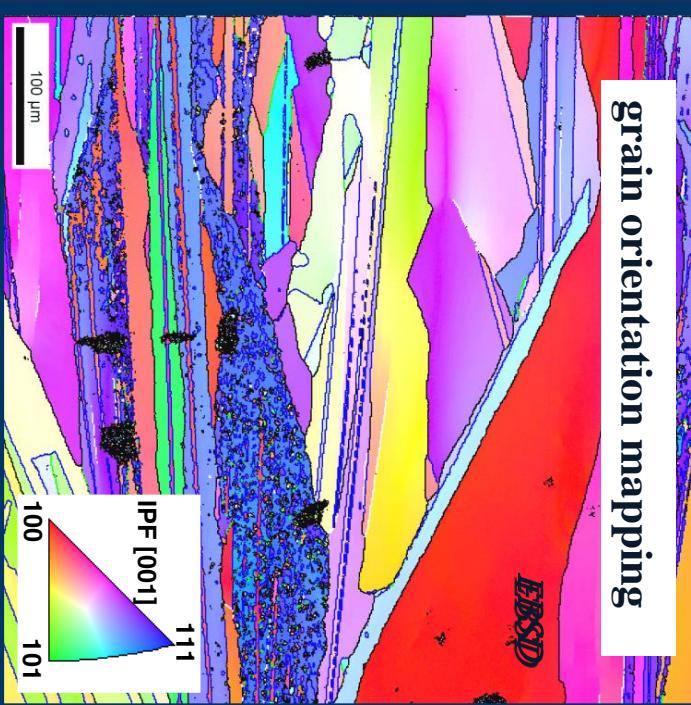
V. Sivakov et al. *Nano Lett.*, 9 (4), 1549–1554 (2009)

# Growth and Analytical Studies on mc-Si

## Seeded Solid phase crystallization

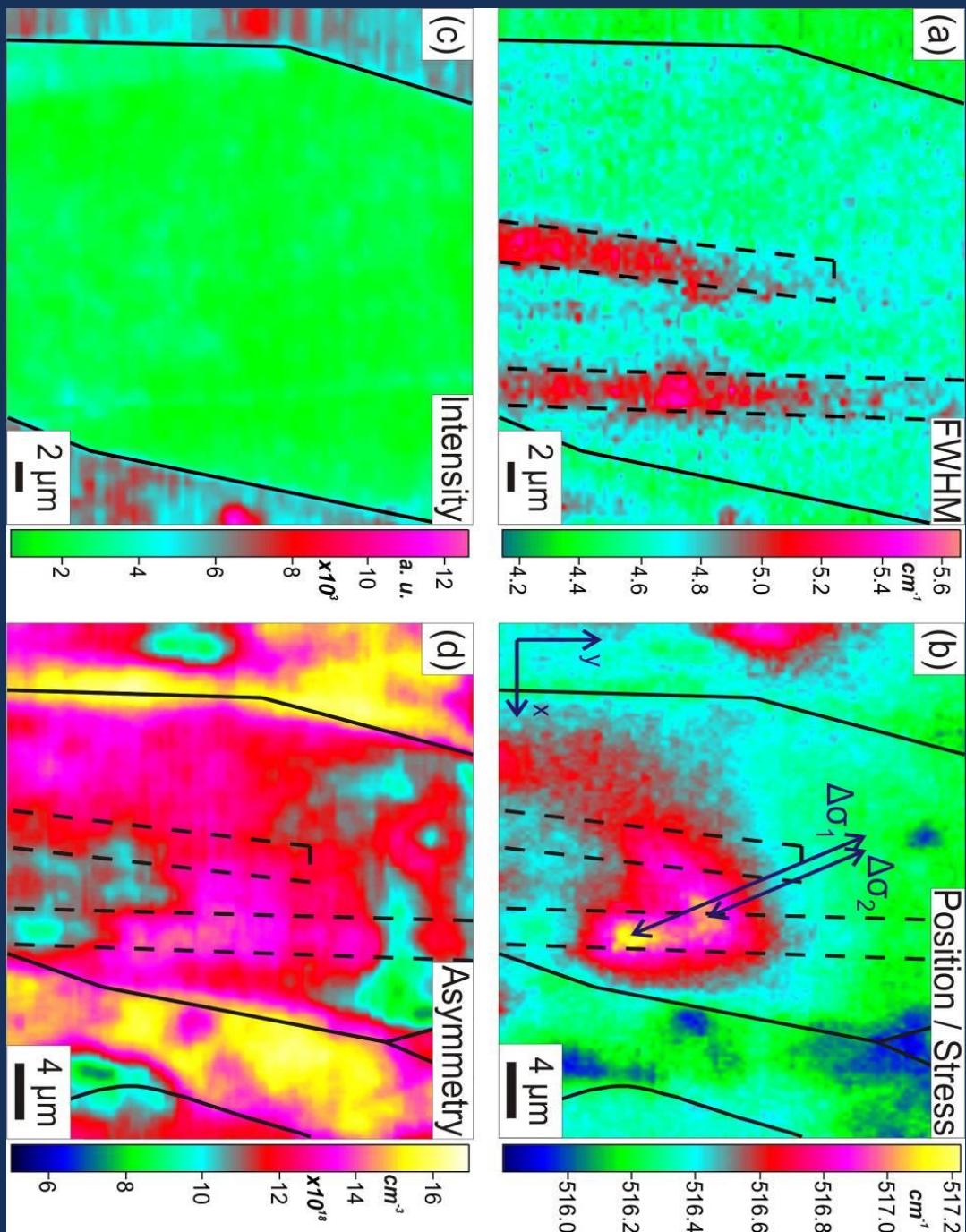


grain orientation mapping



# Growth and Analytical Studies on mc-Si

## Raman Spectroscopy



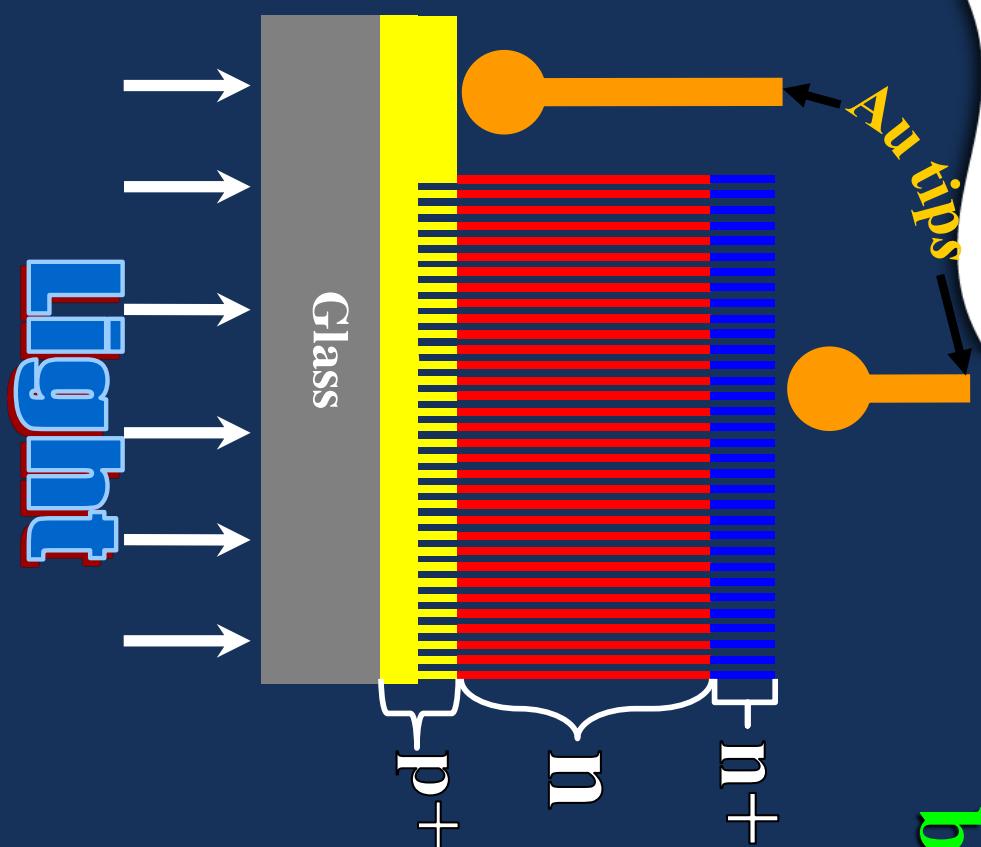
(i) the distribution and qualitative comparison of defect densities;

(ii) amount and sign of internal stresses;

(iii) the grain orientation and the grain boundary pattern;

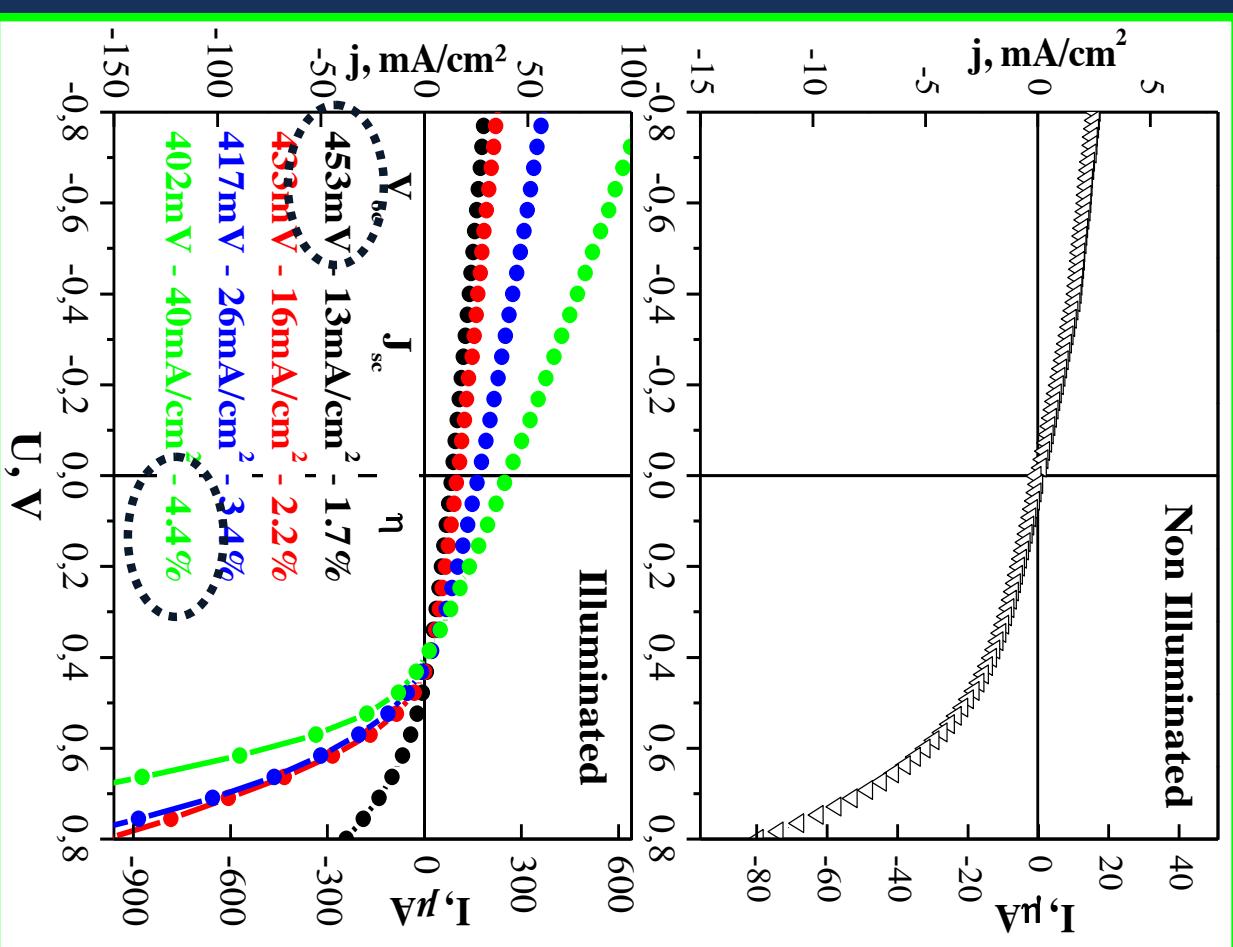
(iv) the distribution and amount of doping.

# PV properties of solar cell based on SiNWs



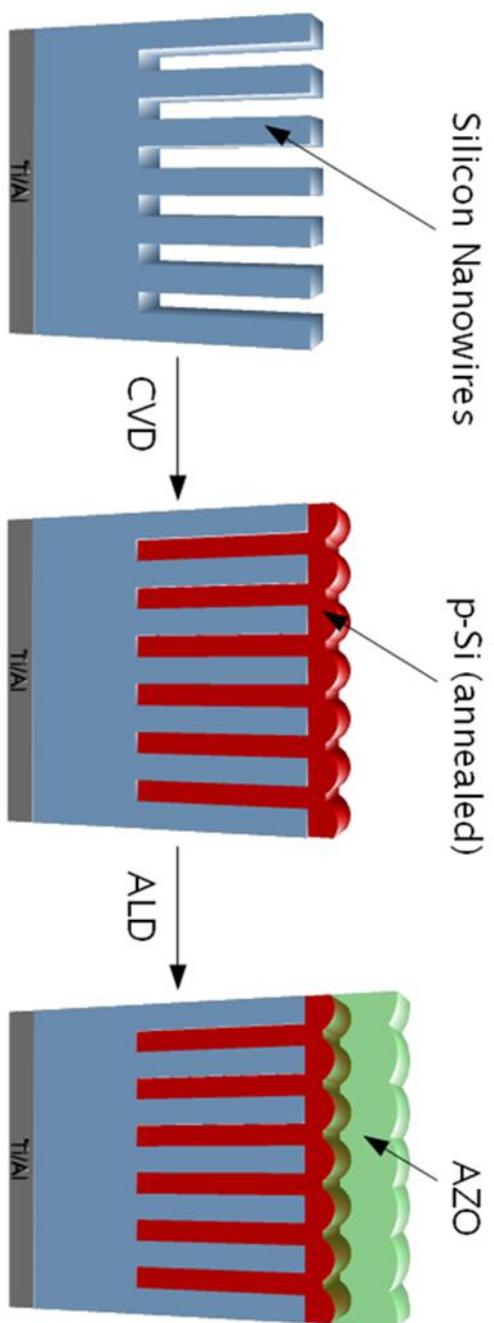
Non illuminated and illuminated (AM1.5) I-V curves of SiNWs etched into a mc-p+nn+-Si layer on glass. SiNW are irradiated through the glass substrate (super-state configuration) and contacted by metal tips at four different sample positions.

V. Sivakov et al. Nano Lett., 9 (4), 1549–1554 (2009)

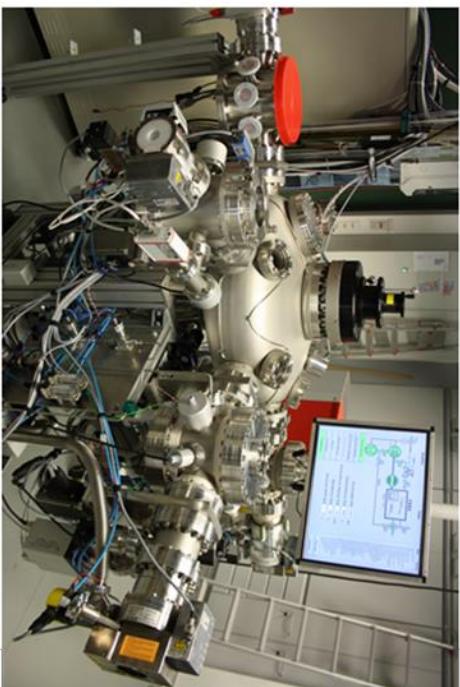


# Photovoltaic Concept III

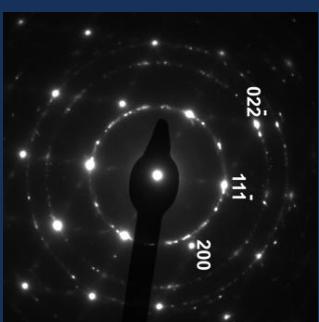
# Realization of Radial p-n junction



- Deposition of Boron-doped a-Si by CVD
- Annealing at  $700^{\circ} \text{ C}$  in order to crystallize/activate the a-Si
- Deposition of AZO by ALD



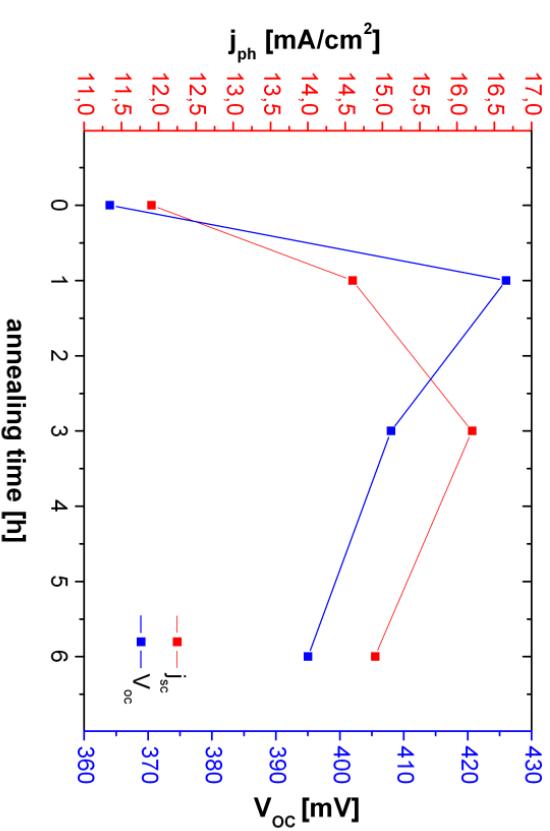
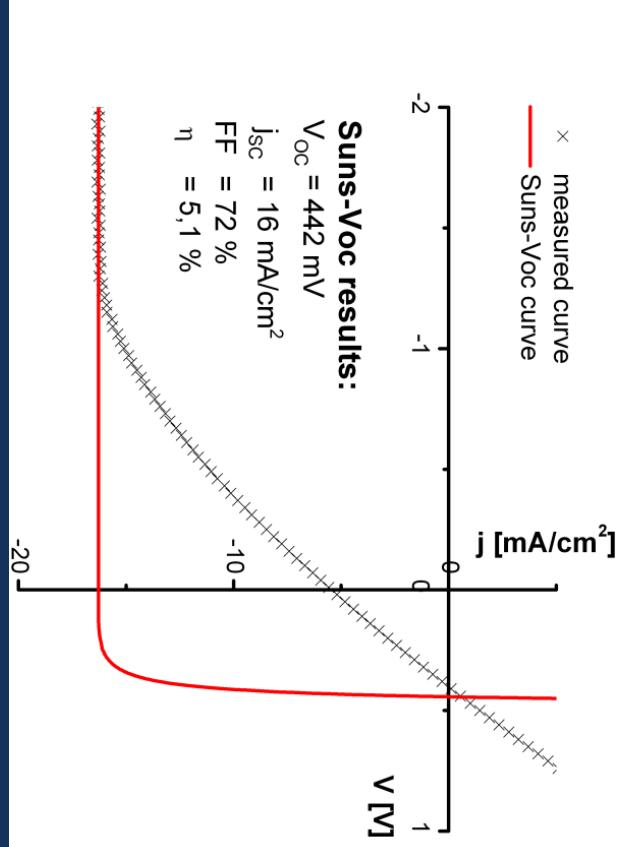
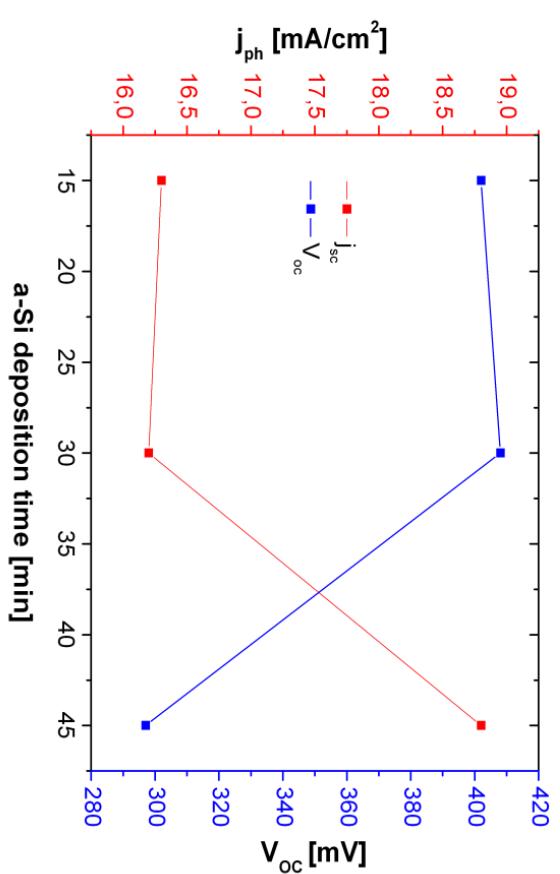
## TEM Studies



- SiNWs are cone-shaped
- a-Si homogeneously covers the SiNWs
- Annealing leads to partial crystallization of the a-Si
- Annealing times of more than three hours do not cause further structural changes

# Realization of Radial p-n junction

- Characterization with I-V- and Suns-Voc-measurements
- Annealing times between one and three hours are optimal
- $j_{sc}$  is relatively low (with respect to the high absorption)
- Efficiencies of 5% could be realized



# Photovoltaic Concept III

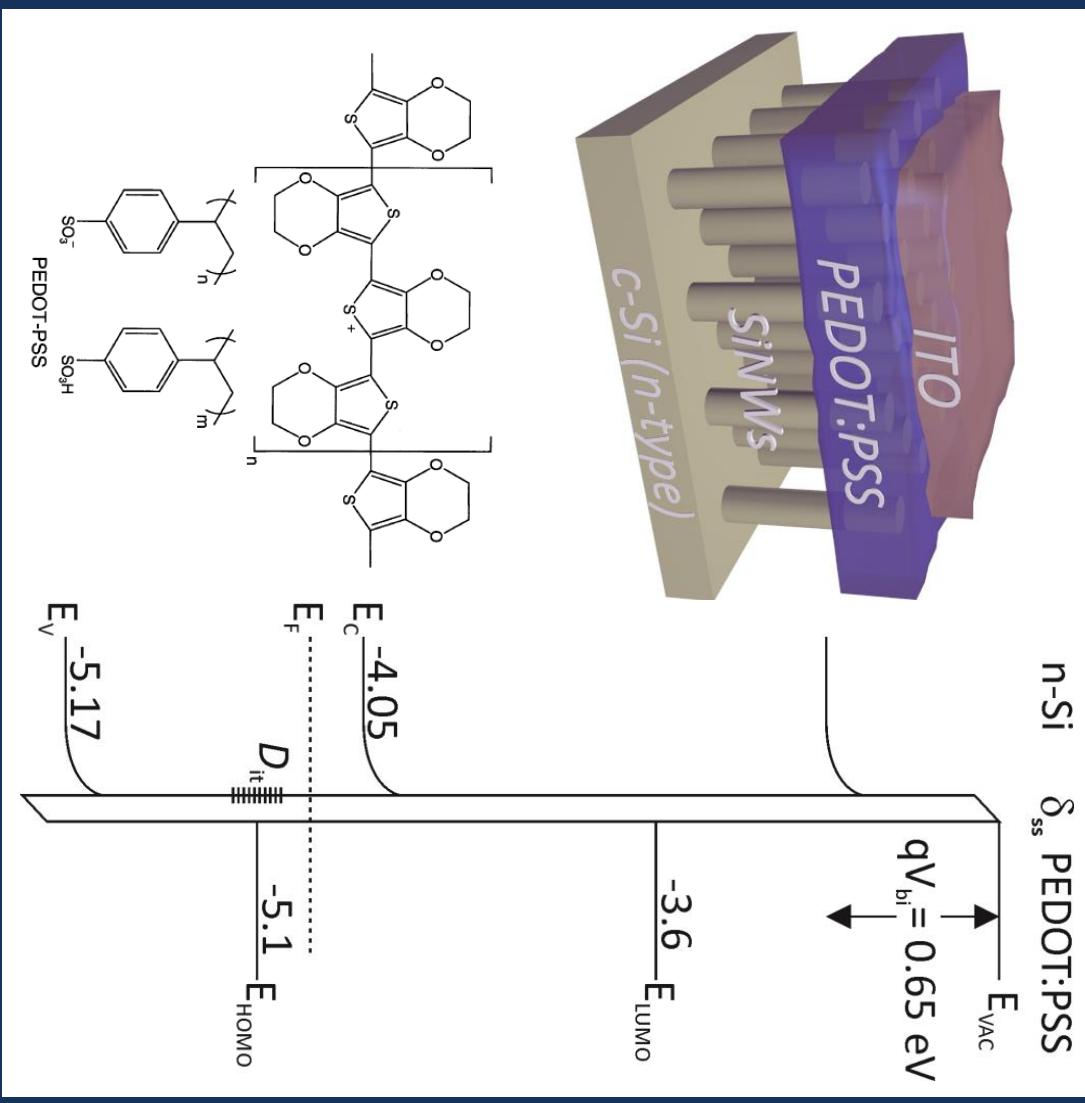
# Hybrid Solar Cells

motivation

- combining high conduction of nanostructured ISC with the ease of processing of OSC
- Low cost processing for high efficient solar cells (aim 10%)
- charge carrier separation at organic/inorganic interface

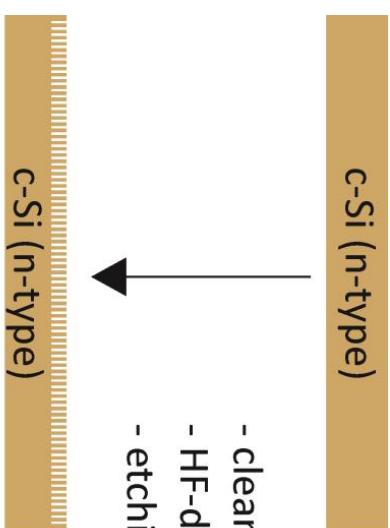
Features of PEDOT:PSS

- many approaches with different polymers
- Advantages of PEDOT:PSS:
  - most stable polymer (chemically and thermally)
  - Conduction is orders of magnitudes higher than for other conjugated polymers

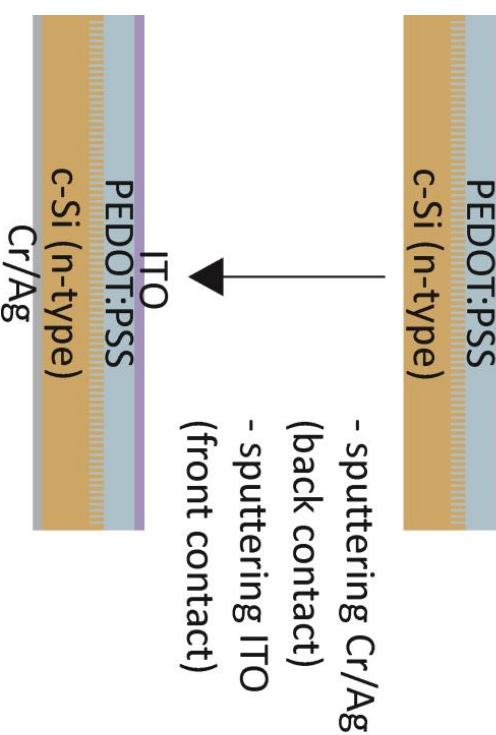


# Hybrid Solar Cell Processing

- Functionalisation of SiNW surfaces is necessary to obtain a hydrophilic surface
- other advantages of surface functionalisation
  - Passivation
  - efficient charge injection

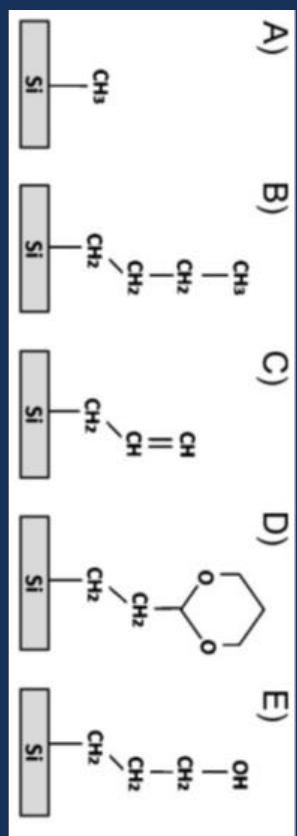
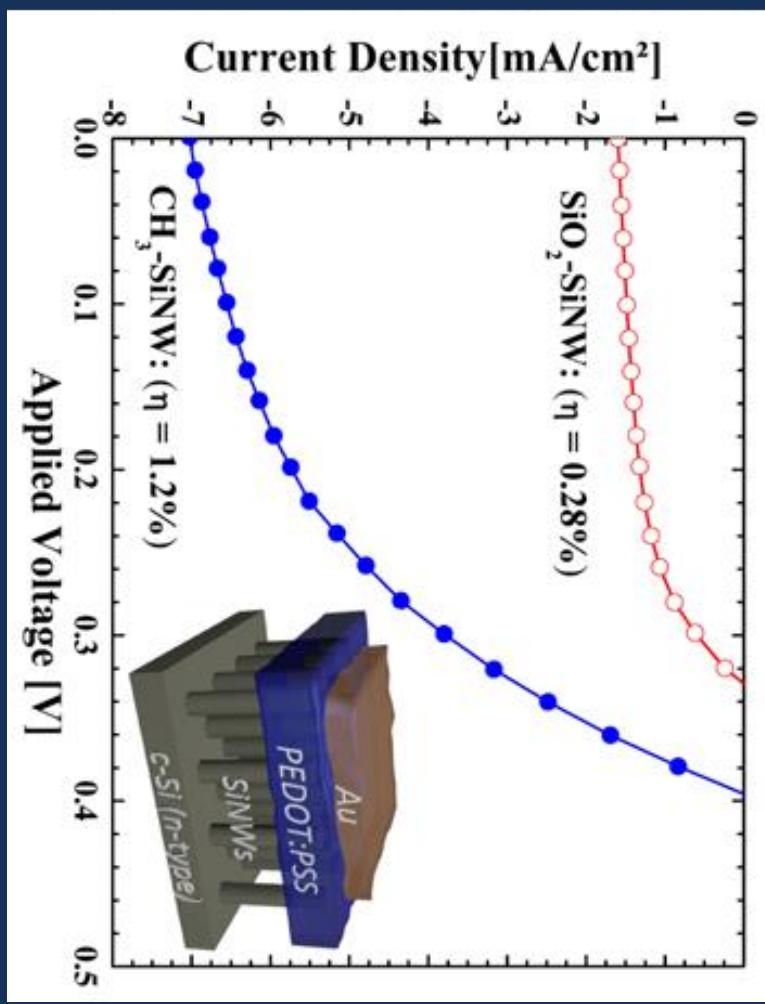
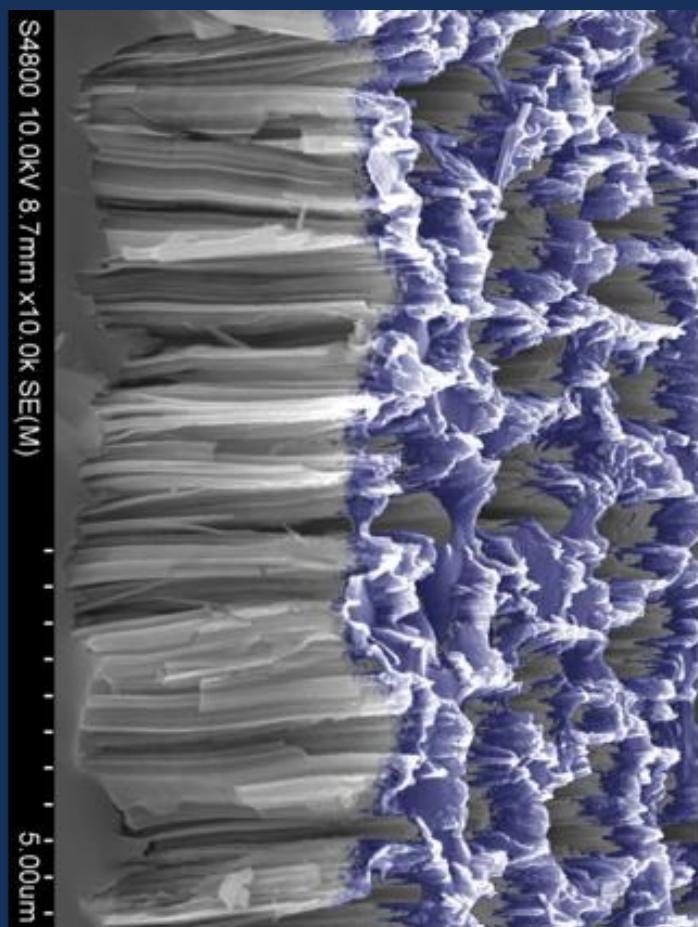


- cleaning wafer
  - HF-dip (5%, 2 min)
  - etching SiNWs
- ↓
- surface functionalisation
  - spin-coating PEDOT:PSS
  - 10 min annealing at 100°C
- ↓



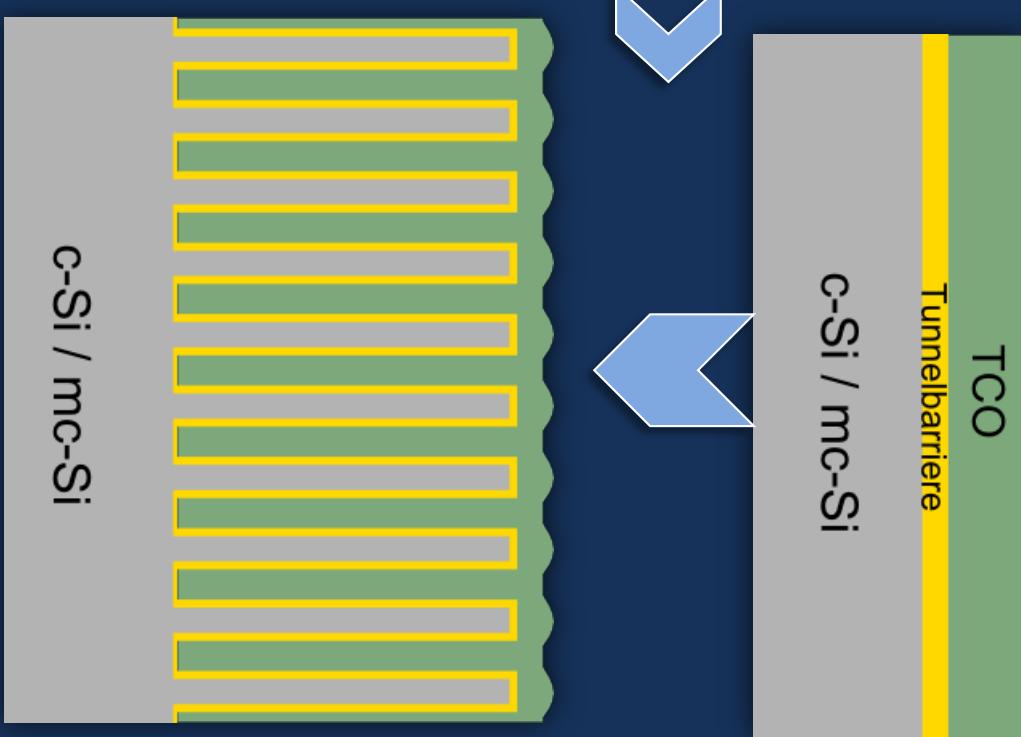
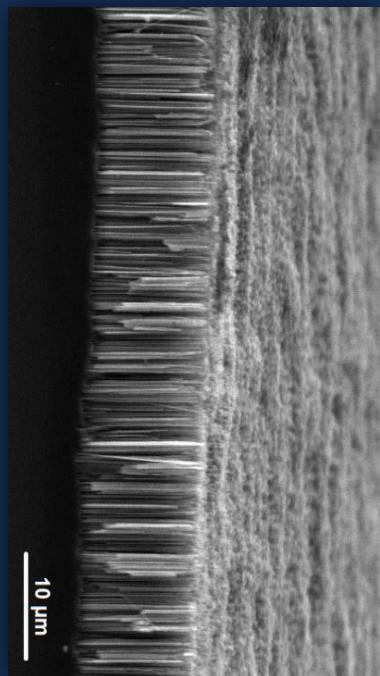
# Functionalization of SiNW surfaces

- Si surface is terminated by covalent bond between Si and C atoms
- different molecules change the surface dipole dramatically (over a range of 0.9 eV)
- Photoelectron Yield Spectroscopy (PYS) reveals higher yield for  $\text{CH}_3$  -terminated SiNWs and reduced density of gap states



# Photovoltaic Concept IV

- Semiconductor-Insulator-Semiconductor
- SiNWs as a light trapping and highly absorbatative material

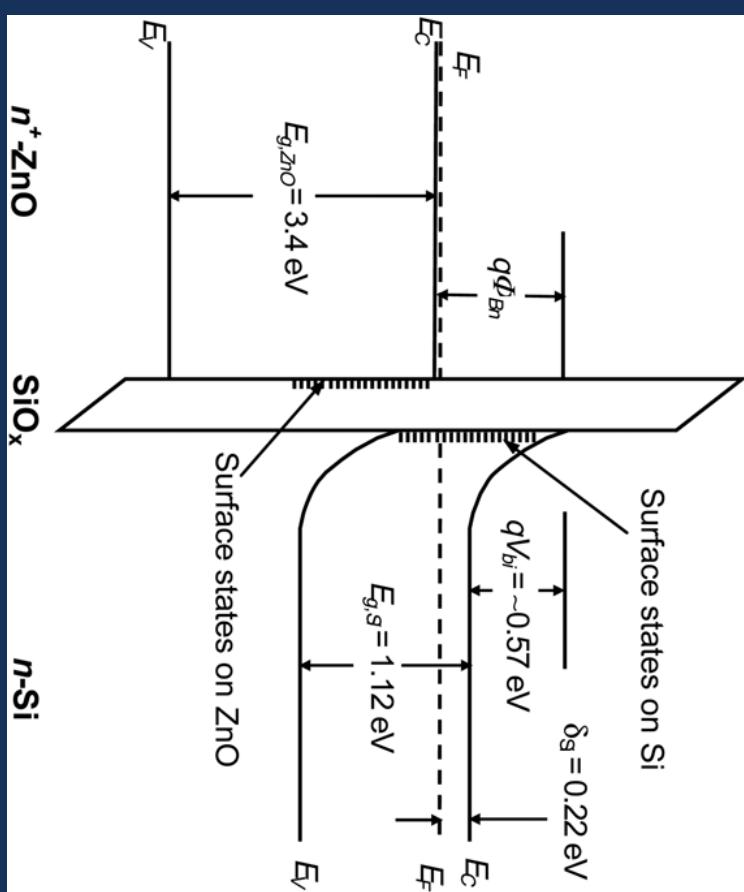


Smart concept



## Background: SiS-Diode

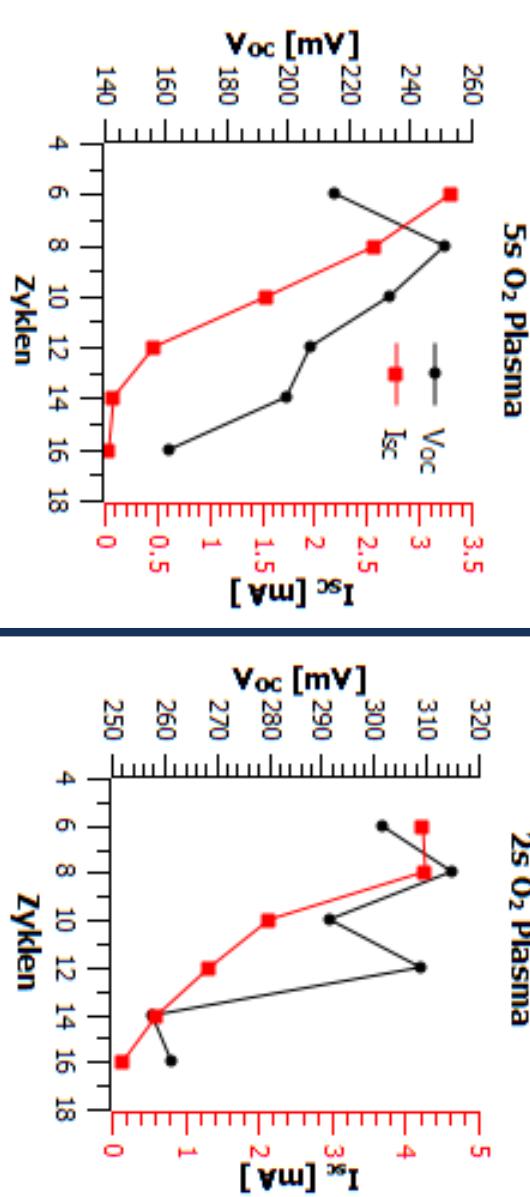
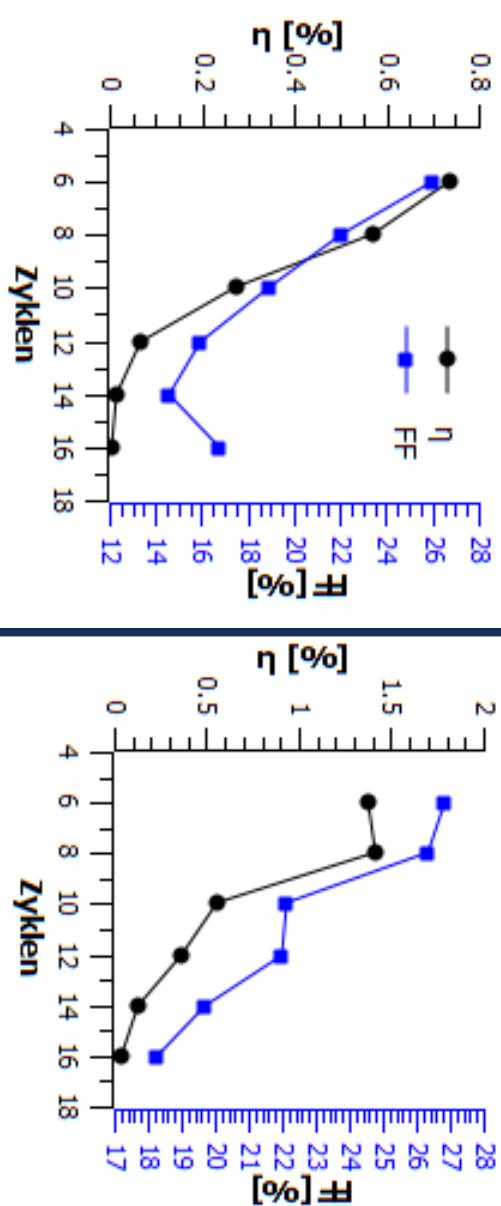
- No pn-junction
- Insert tunnel barrier between both semiconductors  $\rightarrow$  fermi level pinning
- $\rightarrow$  charge carrier separation is based on quantum mechanical tunneling of minority carriers through the barrier



**Challenge:**  
 Transfer the planar wafer-based  
 concept to a nanostructured  
 substrate  
 $\rightarrow$  Reach higher efficiencies  
 because of better light absorption

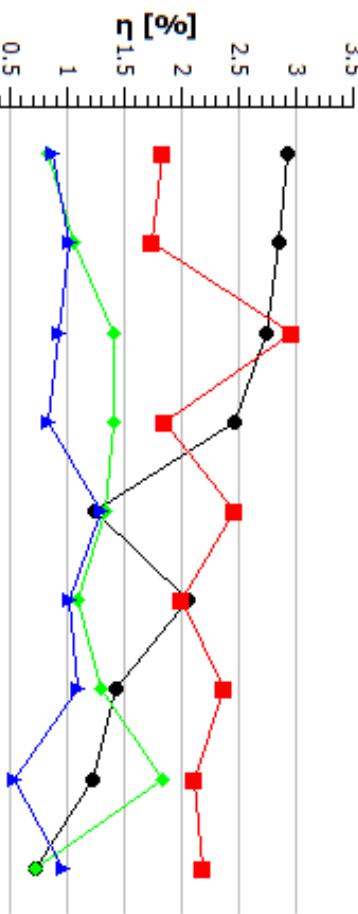
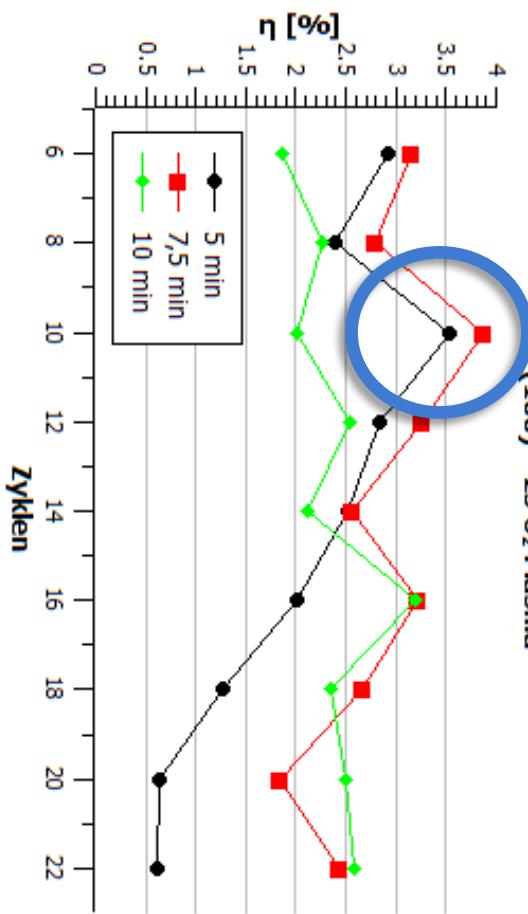
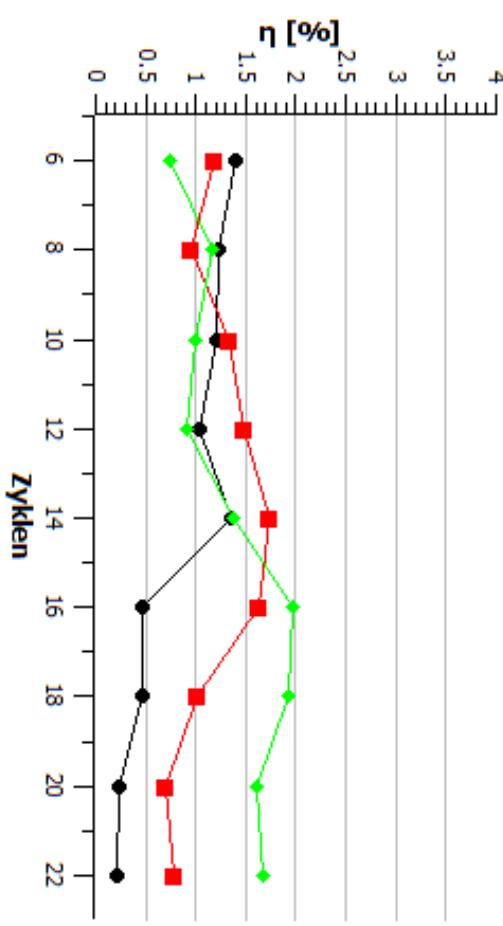
Song, D. & Guo, B. Journal of Physics D: Applied Physics, 2009, 42, 025103  
 V. Sivakov et al., Intech "Nanowires - Fundamental Research", ISBN 978-953-307-327-9, 45-80 (2011)  
 B. Hoffmann, V. Sivakov et al. INTECH "Nanowires - Recent Advances", ISBN: 978-953-51-0898-6, Chapter10 (2012)  
 Dr. Vladimir Sivakov, IPHT

# Planar SIS cells

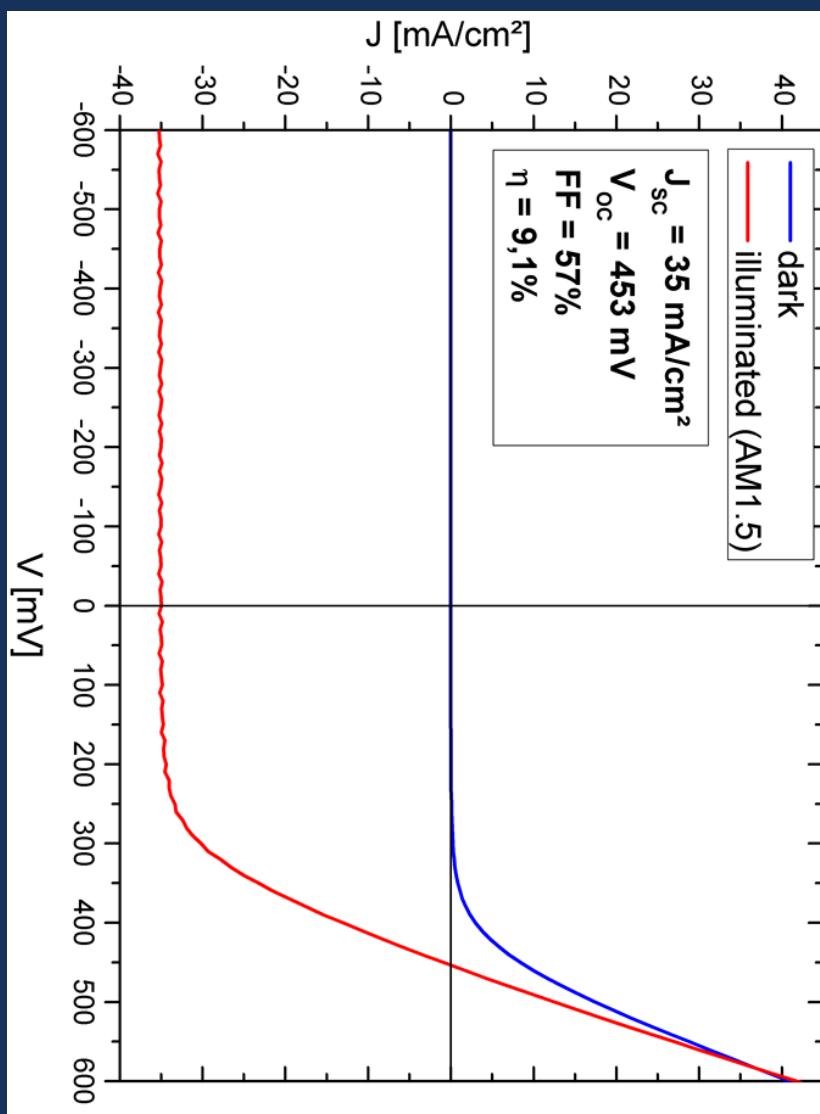
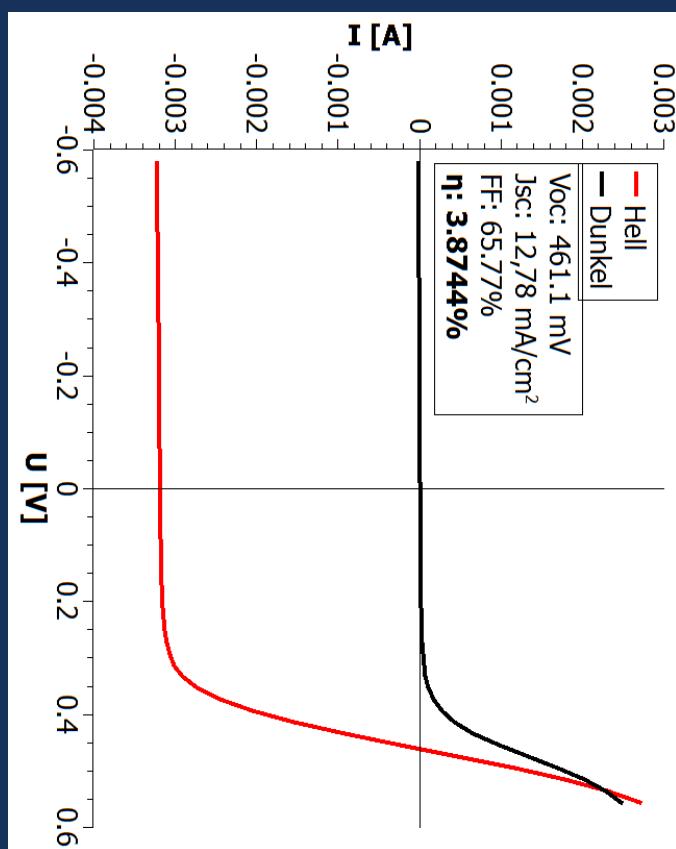


Best Results  
 Voc : 314.7 mV  
 J<sub>SC</sub> : 17.04 mA/cm<sup>2</sup>  
 FF : 26.3 %  
 η : 1.4 %  
 8 Cycle TB  $\cong$  10 Å  
 @ GPC 1,25 Å/Cycle

# Nanowire SIS Cells

(111) - 2s O<sub>2</sub> Plasma(100) - 2s O<sub>2</sub> Plasma(111) - 5s O<sub>2</sub> Plasma(100) - 5s O<sub>2</sub> Plasma

# Best SIS Cells

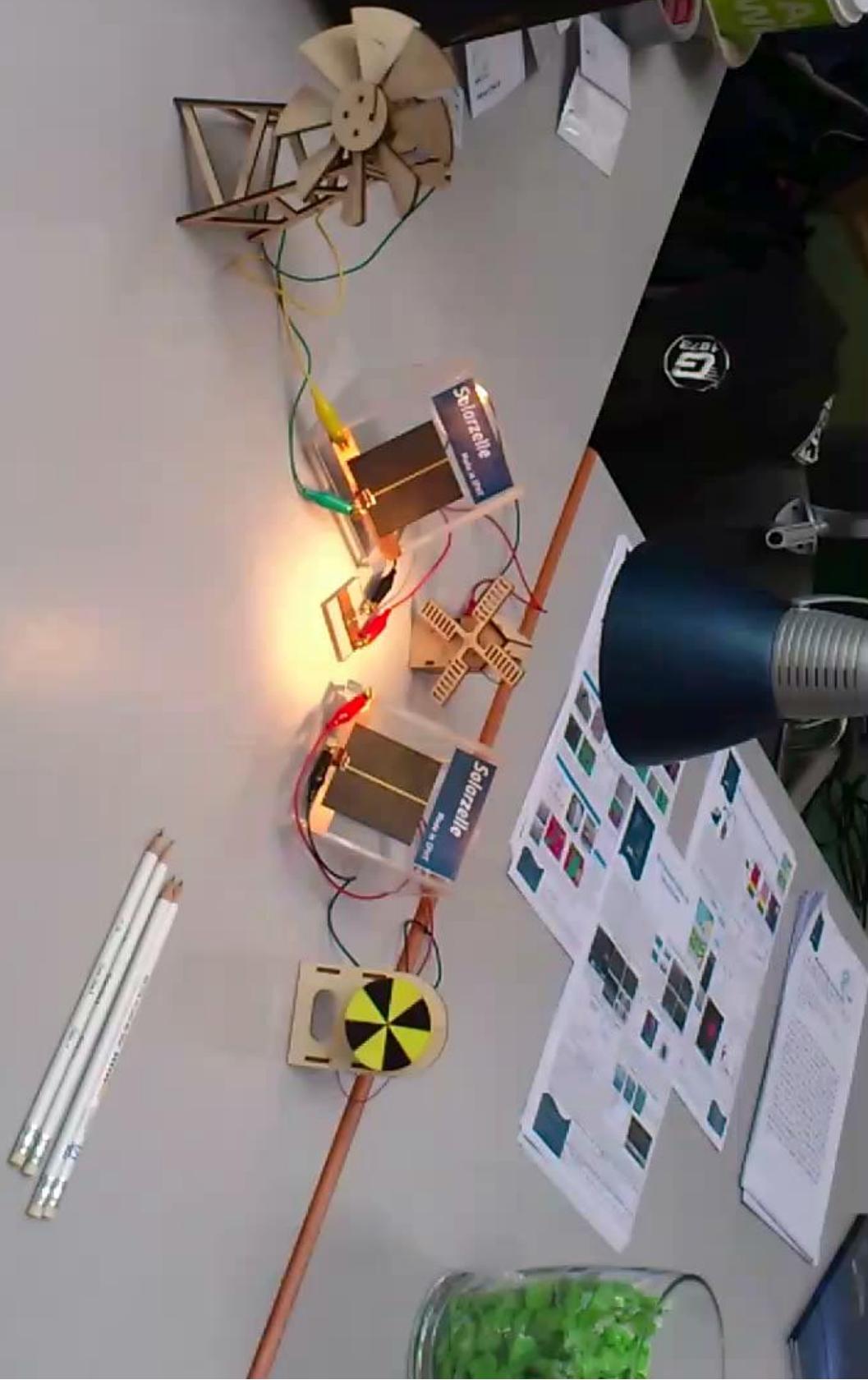


36 cm<sup>2</sup>  
25 mm<sup>2</sup>

# Nanowires based Solar Cell WORKS

Dr. I. Ladinina, IPhT

Silvakov, IPhT



Solar Village

ipht jena

## Newton's Law of Gravity

$$F_g = G \frac{m_1 m_2}{r^2}$$



The famous story that Newton came up with the idea for the law of gravity by having an apple fall on his head is not true, although he did begin thinking about the issue on his mother's farm when he saw an apple fall from a tree.

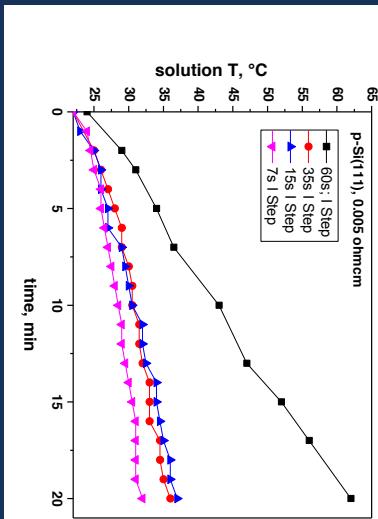
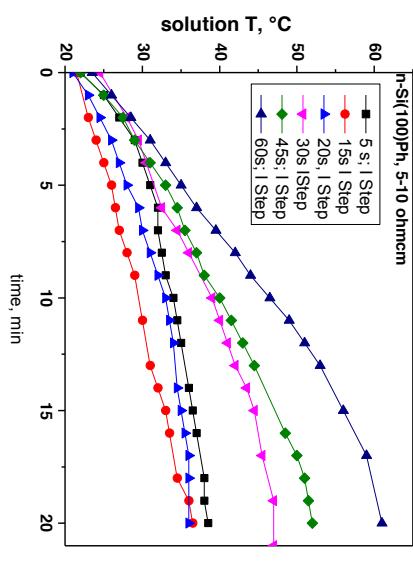


## The Proverbial Apple

*Friedrich August Kekulé* said that he had discovered the ring shape of the benzene molecule after having a reverie or day-dream of a snake seizing its own tail. This vision, he said, came to him after years of studying the nature of carbon-carbon bonds.

## Observation of NATURE!!!!!!

# Energy detachment

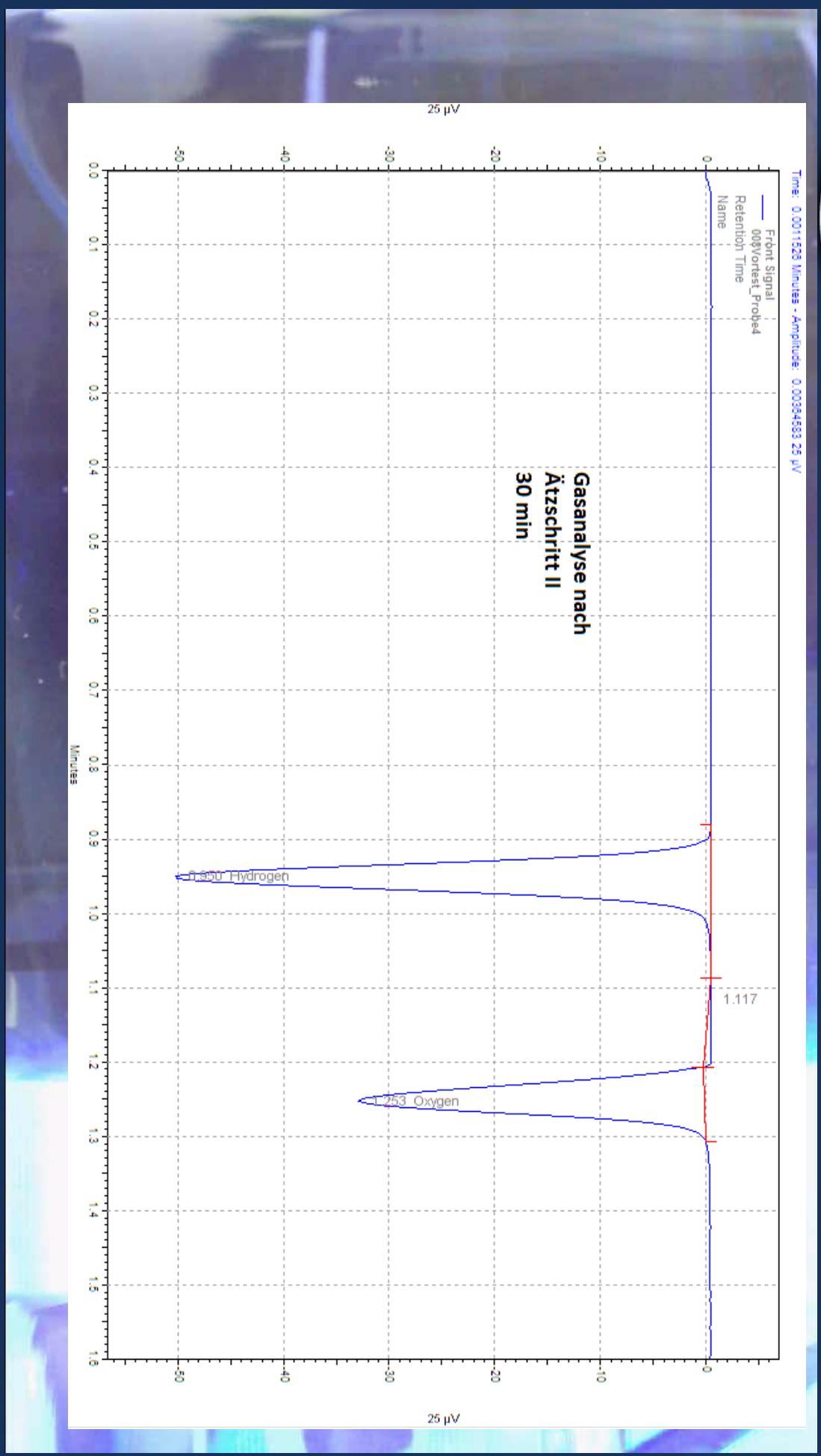


11 H<sub>2</sub>O 1K 4.2 kJ/1.16 Wh

# Observation

>10% Hydrogen!!!

Hydrogen      141,9 MJ/kg  
Oil            46,7 MJ/kg,  
Methanol       23,3 MJ/kg,



# Summary & Outlook

Yes, we can!

Chemical „Black Silicon“ has a big future for photovoltaic, solar fuel, optoelectronic and life science applications.

But, a lot to do.....